

NASA CR 71093

N66-19531

FACILITY FORM 802

(ACCESSION NUMBER)	125	(THRU)	
(PAGES)	CR 71093	(CODE)	14
(NASA CR OR TMX OR AD NUMBER)		(CATEGORY)	

FINAL REPORT
 FOR
 AN EXPERIMENTAL EFFORT TO IMPROVE THE
 NIMBUS HIGH RESOLUTION INFRARED RADIOMETER

VOLUME II OF TWO VOLUMES

(1 May 1964 - 15 February 1965)

Contract No. : NAS 5-3683

Work Order: 65-2-4/65-1-65

Prepared by

ITT Industrial Laboratories
Fort Wayne, Indiana

For

National Aeronautics & Space Administration
Aeronomy and Meteorology Branch
Goddard Space Flight Center
Greenbelt, Maryland

GPO PRICE \$ _____

CFSTI PRICE(S) \$ _____

Hard copy (HC) 4.00

Microfiche (MF) 1.00

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Contributors

W. H. Wallschlaeger, P. C. Murray,
P. R. Sargent, R. V. Annable

Approved by



W. H. Wallschlaeger,
Project Manager



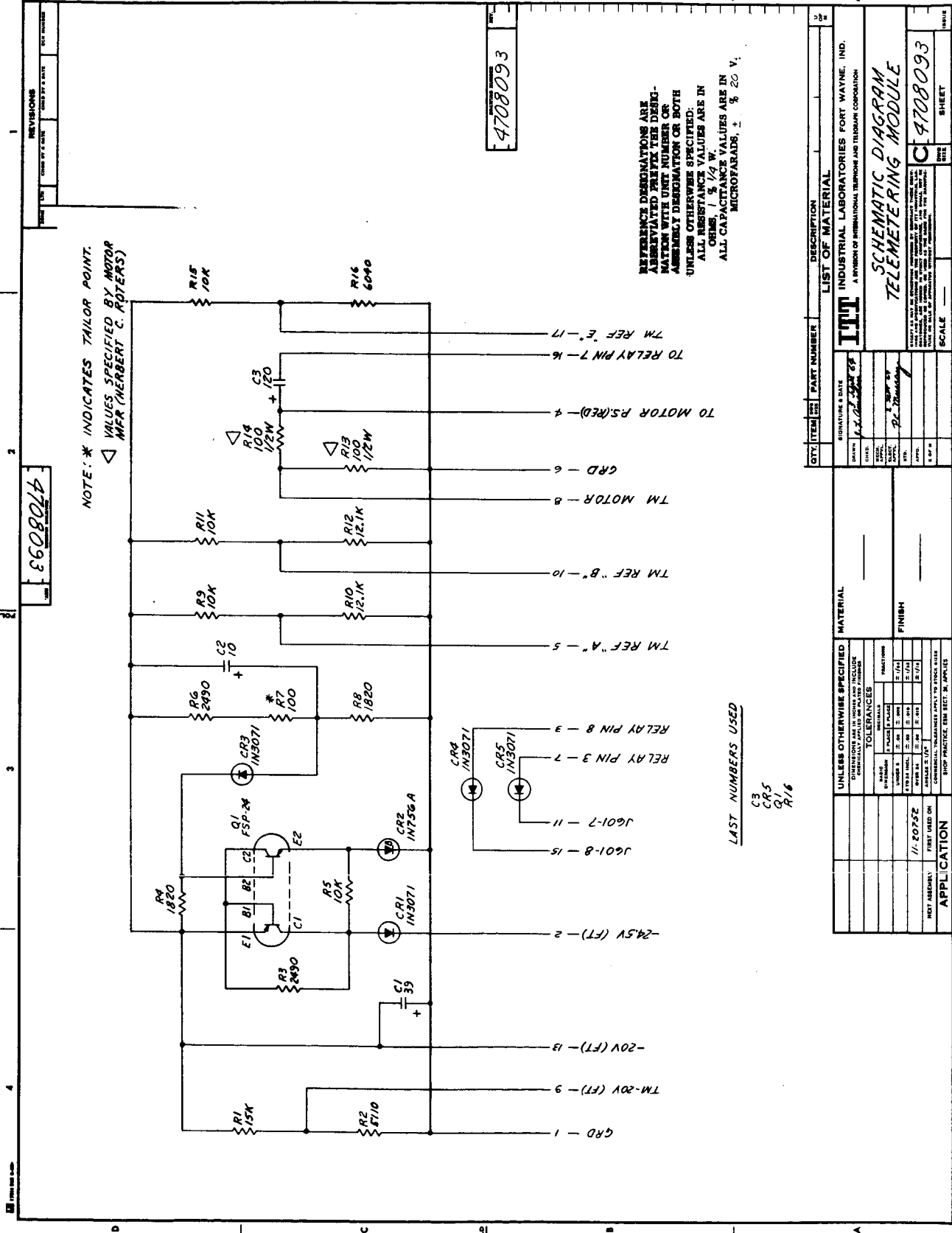
K. L. DeBrosse, Manager
Space & Physical Sciences Dept.

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APPENDIX I

DRAWINGS



4708093

NOTE: * INDICATES TAYLOR POINT.
 ▽ VALUES SPECIFIED BY MOTOR MFR (HERBERT C. ROTERS)

REFERENCE DESIGNATIONS ARE ABBREVIATED PER THE DESIGNATION WITH UNIT NUMBER OR ASSEMBLY DESIGNATION OR BOTH UNLESS OTHERWISE SPECIFIED:
 ALL RESISTANCE VALUES ARE IN OHMS, 1/4 W.
 ALL CAPACITANCE VALUES ARE IN MICROFARADS, ± 5% 20 V.

LAST NUMBERS USED
 C3
 CR5
 R16

4708093

QTY.	ITEM	DESCRIPTION	PART NUMBER	REVISIONS
		INDUSTRIAL LABORATORIES FORT WAYNE, IND.		
		A DIVISION OF INTERNATIONAL TELEPHONE AND TELEGRAPH CORPORATION		
		SCHEMATIC DIAGRAM		
		TELEMETERING MODULE		
		SCALE		
		SHEET		
		4708093		

SIGNATURE & DATE		MATERIAL	
DATE	BY	FINISH	
1.1.58	PE		

UNLESS OTHERWISE SPECIFIED		DIMENSIONS ARE IN INCHES AND INCLUDE TOLERANCES	
FINISH		FINISH	

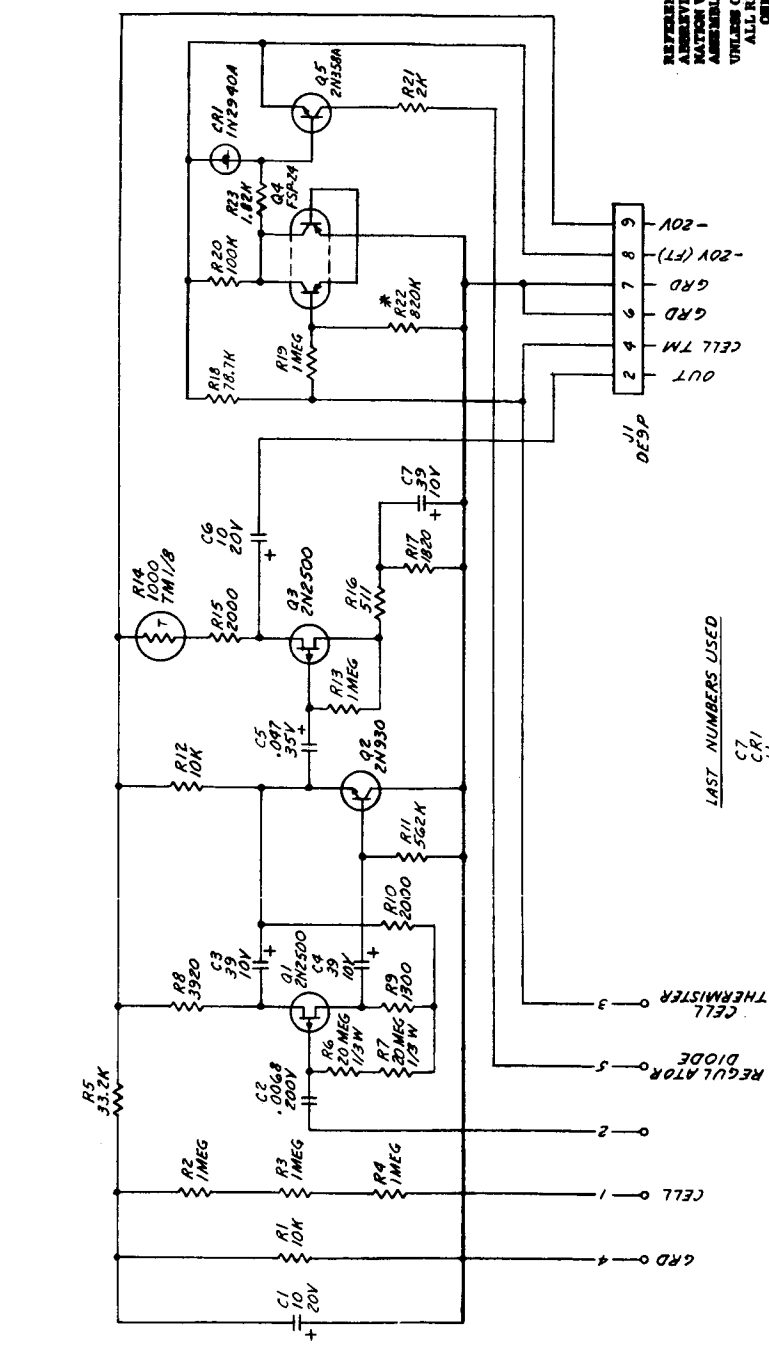
APPLICATION	
DATE	BY
11-20-52	

REV	DATE BY	CHK BY	REV

REVISIONS

4708090

- NOTES:
- * INDICATES TAILOR POINT.
 - OMIT R1 FOR 20V CELL BIAS.



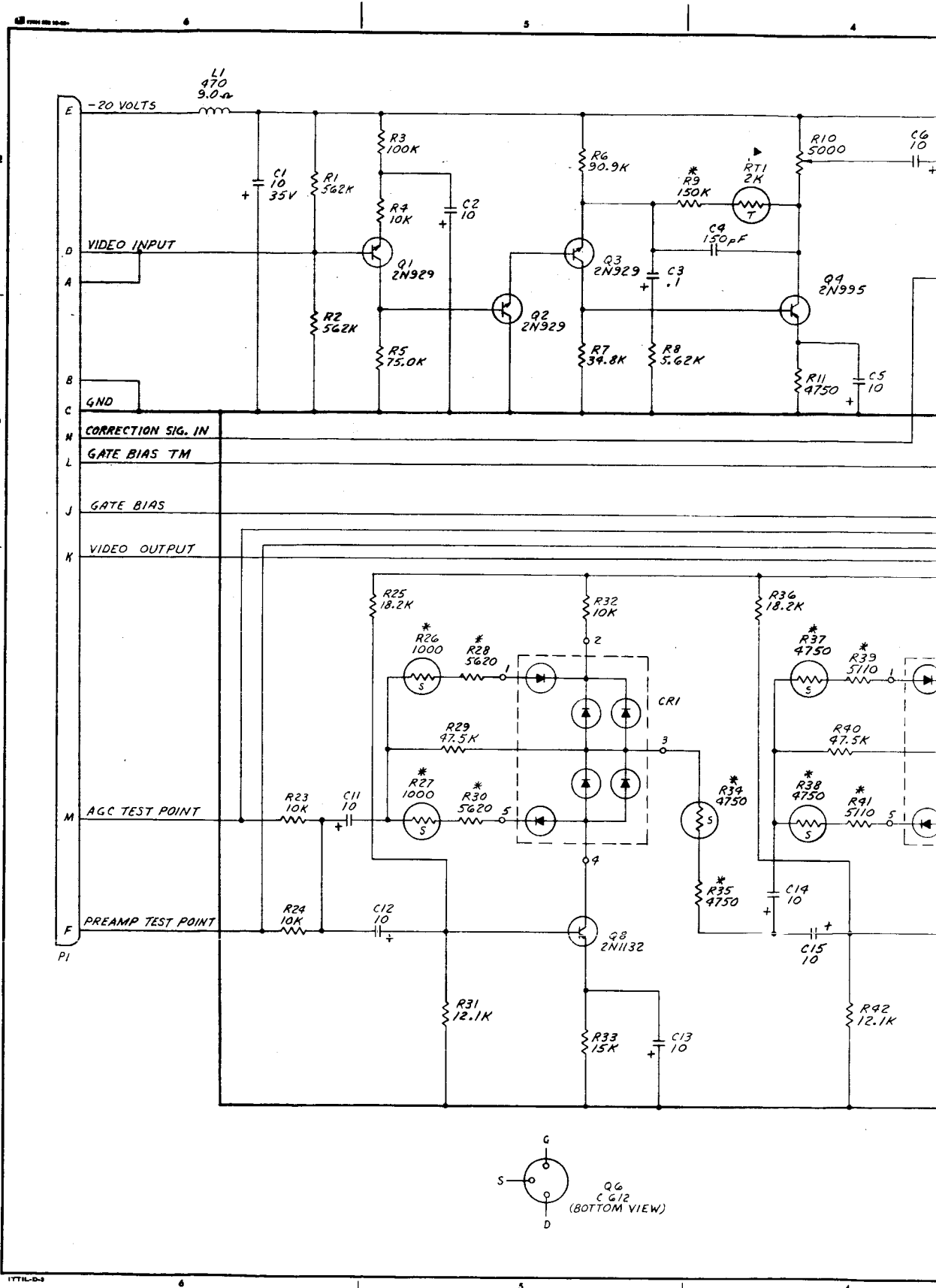
REFERENCE DESIGNATIONS ARE
ABBREVIATED PER THE DESIG-
NATION WITH UNIT NUMBER OR
ASSEMBLY DESIGNATION OR BOTH
UNLESS OTHERWISE SPECIFIED.
ALL RESISTANCE VALUES ARE IN
OHMS UNLESS OTHERWISE SPECIFIED.
ALL CAPACITANCE VALUES ARE IN
MICROFARADS.

LAST NUMBERS USED

- C7
- CRI
- J1
- Q5
- R23

4708090

QTY.		ITEM	PART NUMBER	DESCRIPTION
LIST OF MATERIAL				
INDUSTRIAL LABORATORIES FORT WAYNE, IND.				
A DIVISION OF INDUSTRIAL THERMO AND THERMO CORP.				
SCHEMATIC DIAGRAM				
LOW-NOISE PREAMPLIFIER (6-VOLT)				
SCALE				
SHEET				
4708090				



4 ①

660801b

REVISIONS

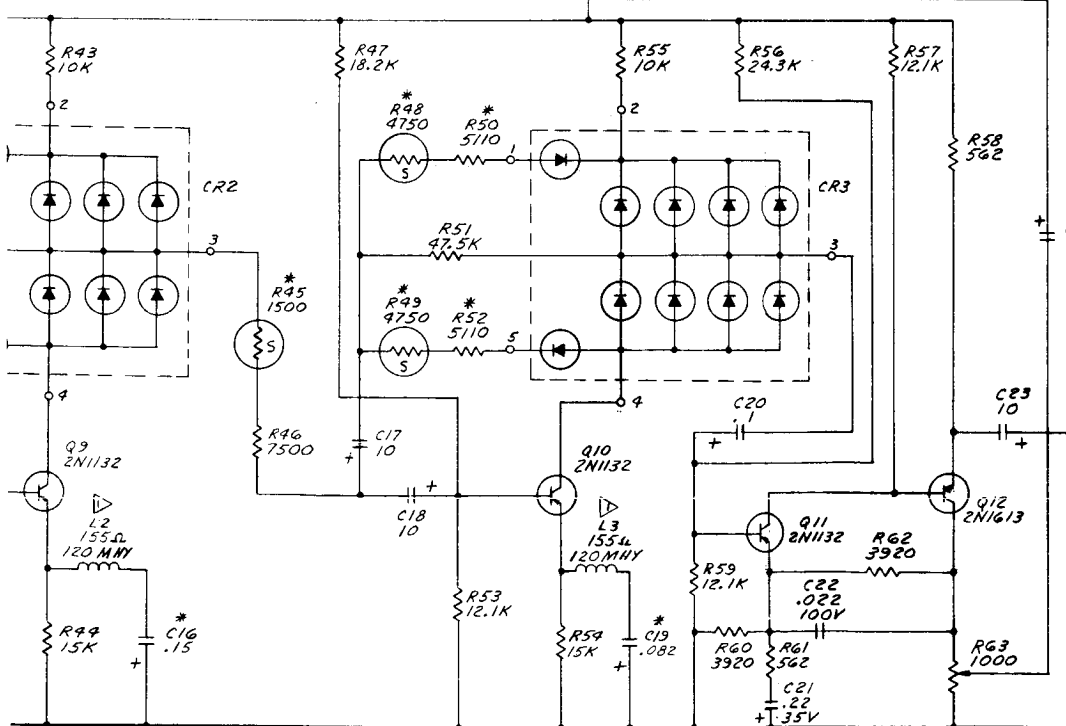
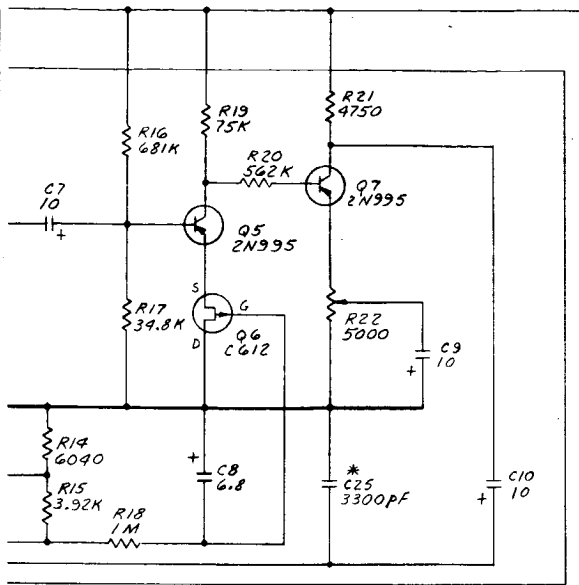
DATE	BY	CHKD BY	DATE	REV

REFERENCE DESIGNATIONS ARE ABBREVIATED PREFIX THE DESIGNATION WITH UNIT NUMBER OR ASSEMBLY DESIGNATION OR BOTH

UNLESS OTHERWISE SPECIFIED:
 ALL RESISTANCE VALUES ARE IN OHMS, % W.
 ALL CAPACITANCE VALUES ARE IN MICROFARADS, % V.
 ALL DIMENSIONAL VALUES ARE IN MILLIMETERS.

NOTE: ▷ INDICATES FENVAL 6832P92A-T2 THERMISTOR.
 * DENOTES TAILORING POINT.
 ▷ UTC MM-8

LAST NO. USED	NO. NOT USED
C25	R12
CR3	R13
L3	
P1	
Q12	
Q53	
R77	



4708099

UNLESS OTHERWISE SPECIFIED		MATERIAL	
DIMENSIONS ARE IN INCHES AND INCLUDE CHEMICALLY APPLIED OR PLATED FINISHES			
TOLERANCES			
BASIC DIMENSION	DECIMALS	FRACTIONS	FINISH
UNDER .4	± .01	± .005	± 1/32
.4 TO 1.4 INCL.	± .01	± .010	± 1/32
OVER 1.4	± .02	± .015	± 1/16
ANGLE ± 1/2°			
COMMERCIAL TOLERANCES APPLY TO STOCK SIZES			
SHOP PRACTICE, ESM SECT. 38, APPLIES			

QTY.	ITEM	REV.	PART NUMBER	DESCRIPTION

LIST OF MATERIAL

INDUSTRIAL LABORATORIES FORT WAYNE, IND.
 A DIVISION OF INTERNATIONAL TELEPHONE AND TELEGRAPH CORPORATION

SCHEMATIC DIAGRAM VIDEO BOARD

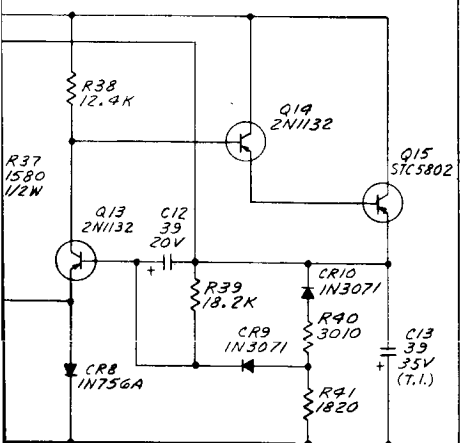
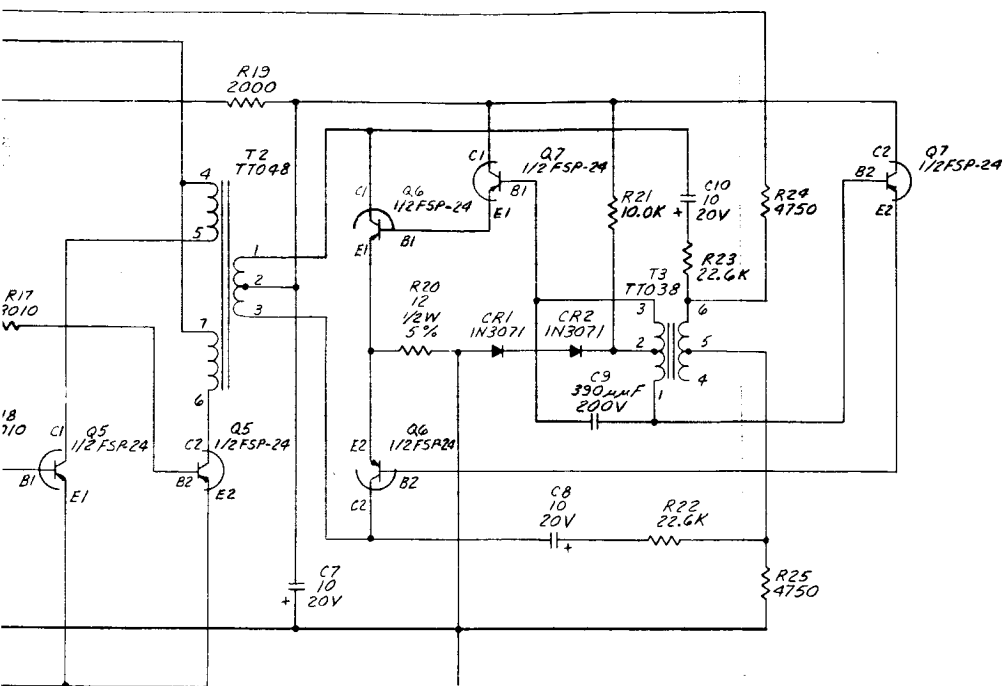
4708099

SHEET

2

EE1801D
 SECOND QUARTER

REVISIONS			
ZONE	LTN	CHG BY & DATE	ECN NUMBER



NOTES:
 * DESIGNATES TAILORING POINT.

REFERENCE DESIGNATIONS ARE ABBREVIATED PREFIX THE DESIGNATION WITH UNIT NUMBER OR ASSEMBLY DESIGNATION OR BOTH
 UNLESS OTHERWISE SPECIFIED:
 ALL RESISTANCE VALUES ARE IN OHMS, 1/4 W.
 ALL CAPACITANCE VALUES ARE IN MICROFARADS, ±10% 100 V

4708133

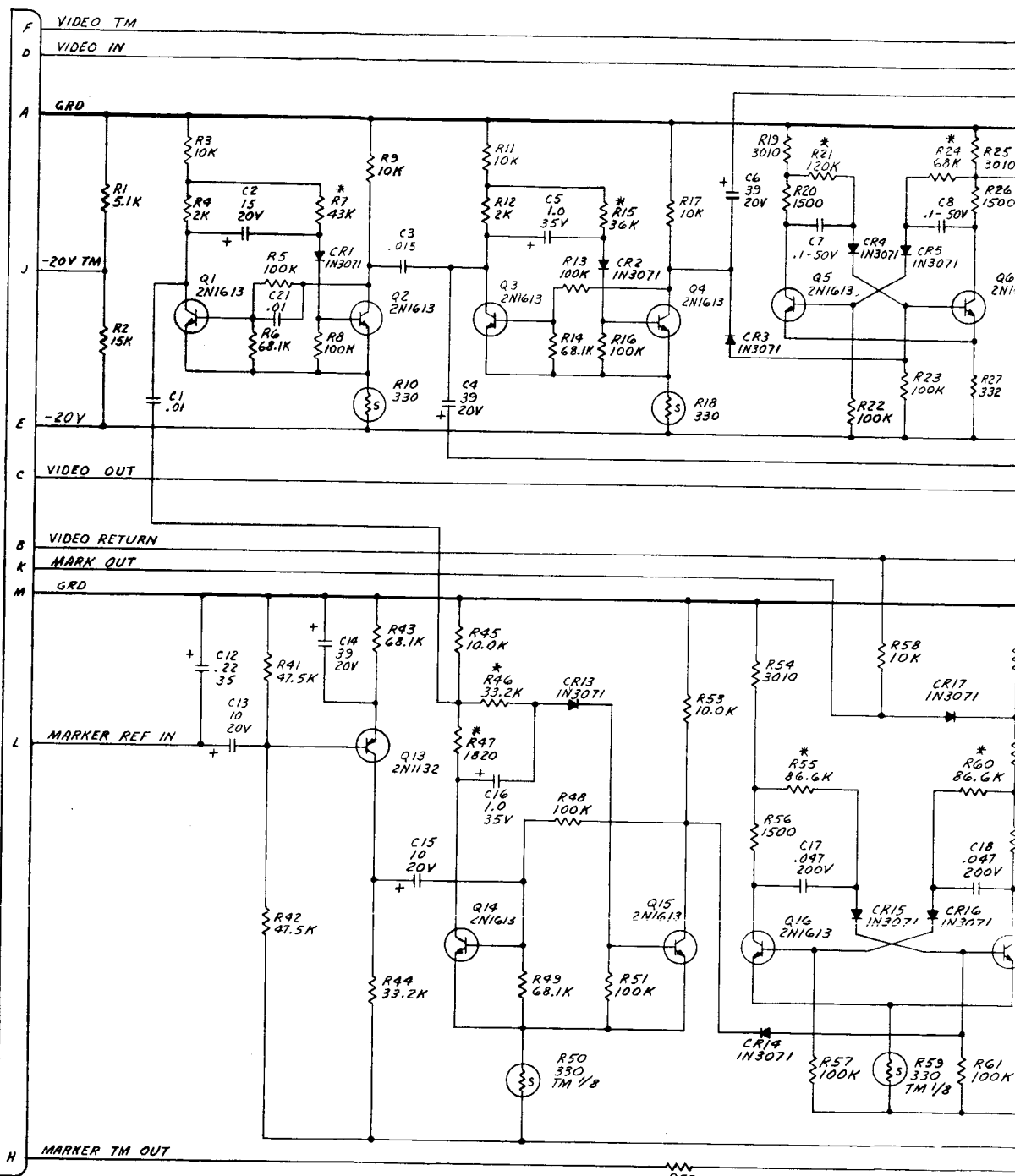
T USED

QTY.	ITEM	SIZE	PART NUMBER	DESCRIPTION	SEC OF
LIST OF MATERIAL					
ITT INDUSTRIAL LABORATORIES FORT WAYNE, IND.					
A DIVISION OF INTERNATIONAL TELEPHONE AND TELEGRAPH CORPORATION					
SIGNATURE & DATE				SCHEMATIC DIAGRAM OUTPUT-POWER-AGC BOARD	
DRAWN <i>S. D. C. 1/28/53</i>					
CHECKED					
DESIGNED					
ELECT. ENG.					
APP'D					
E. OF M.				D 4708133	
SCALE					
PWB SIZE				SHEET	

UNLESS OTHERWISE SPECIFIED		MATERIAL	
DIMENSIONS ARE IN INCHES AND INCLUDES CHEMICALLY APPLIED OR PLATED FINISHES			
TOLERANCES			
BASIC DIMENSION	DECIMALS	FRACTIONS	FINISH
UNDER 8	±.005	± 1/32	
8 TO 24 INCL	±.010	± 1/16	
OVER 24	±.015	± 1/8	
ANGLES ±.25°			
COMMERCIAL TOLERANCES APPLY TO STOCK USED			
SHOP PRACTICE, ESM SECT. 38, APPLIES			

NEXT ASSEMBLY	FIRST USED ON
APPLICATION	11-20753

2



P1 (11 PIN)

LAST NO. USED	NO. NOT USED
C21	CR6
CR19	R36
P1	
Q18	
R10	

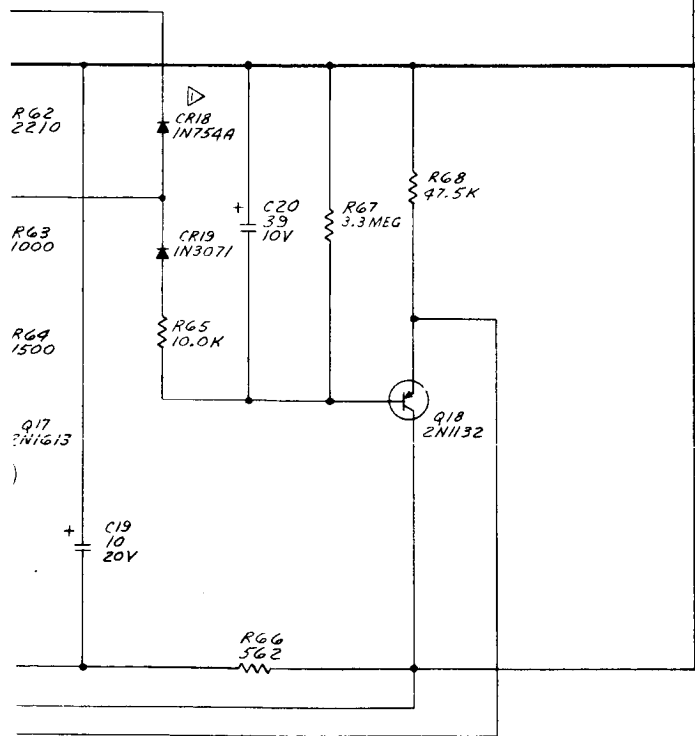
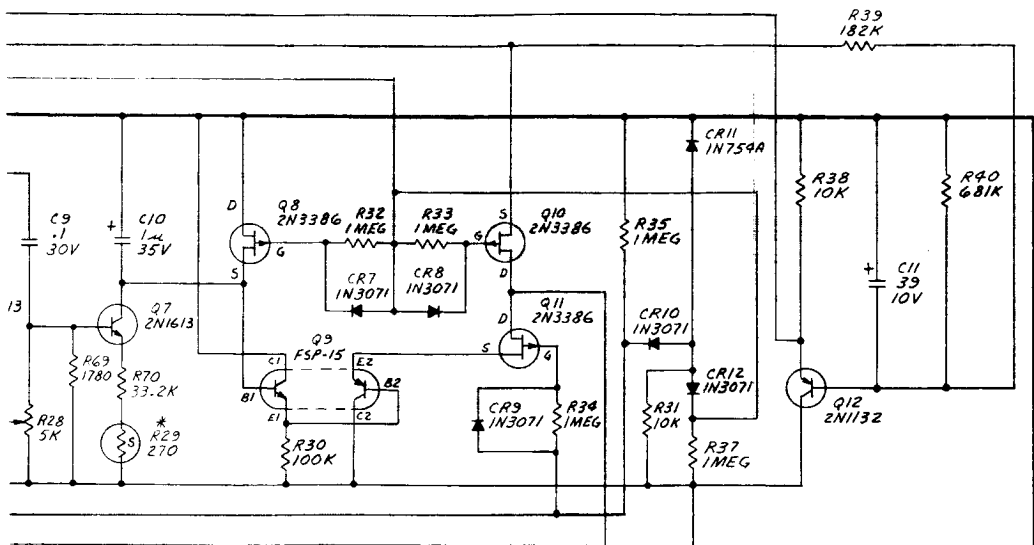
R52 1K

6 ①

161801b

REVISIONS

ZONE	LTR	CHD BY & DATE	CHD BY & DATE	ECN NUMBER



NOTES:
 * DESIGNATES TAILORING POINT.
 ▽ SELECTED FOR 5.75 ± .25 VDC @ 1.25 ma.

4708/41

REFERENCE DESIGNATIONS ARE
 ABBREVIATED PREFIX THE DESIG-
 NATION WITH UNIT NUMBER OR
 ASSEMBLY DESIGNATION OR BOTH
 UNLESS OTHERWISE SPECIFIED:
 ALL RESISTANCE VALUES ARE IN
 OHMS, 1/4 W.
 ALL CAPACITANCE VALUES ARE IN
 MICROFARADS, 1/10 W, 100 V.

UNLESS OTHERWISE SPECIFIED		MATERIAL	
DIMENSIONS ARE IN INCHES AND INCLUDE CHEMICALLY APPLIED OR PLATED FINISHES			
TOLERANCES			
BASIC DIMENSION	DECIMALS	FRACTIONS	FINISH
UNDER .4	± .04	± 1/64	
.4 TO .49 INCL	± .04	± 1/32	
OVER .49	± .04	± 1/16	
HOLE SIZE 1/16			
COMMERCIAL TOLERANCES APPLY TO STOCK SIZES			
SHOP PRACTICE, ESM SECT. 3A, APPLIES			

QTY.	ITEM	SIZE	PART NUMBER	DESCRIPTION	REV.	NO. OF SHEETS
LIST OF MATERIAL						
SIGNATURE & DATE						
DRAWN <i>J. J. O'Connell</i> 26 07 49						
CHKD.						
ELECT. LABEL						
BTO.						
APPRO.						
E OF W.						
EXCEPT AS MAY BE OTHERWISE PROVIDED BY CONTRACT THESE DIMENSIONS AND SPECIFICATIONS ARE THE PROPERTY OF ITT INDUSTRIAL LABORATORIES AND SHALL NOT BE REPRODUCED OR COPIED, OR USED AS THE BASIS FOR THE MANUFACTURE OR SALE OF APPARATUS WITHOUT PERMISSION.						
SCALE					REV. 4708/41	ISSUE

ITT INDUSTRIAL LABORATORIES FORT WAYNE, IND. A DIVISION OF INTERNATIONAL TELEPHONE AND TELEGRAPH CORPORATION

SCHMATIC DIAGRAM CALIBRATOR-MARKER GENERATOR

4708/41

APPLICATION

11-20753

SHEET

ISSUE

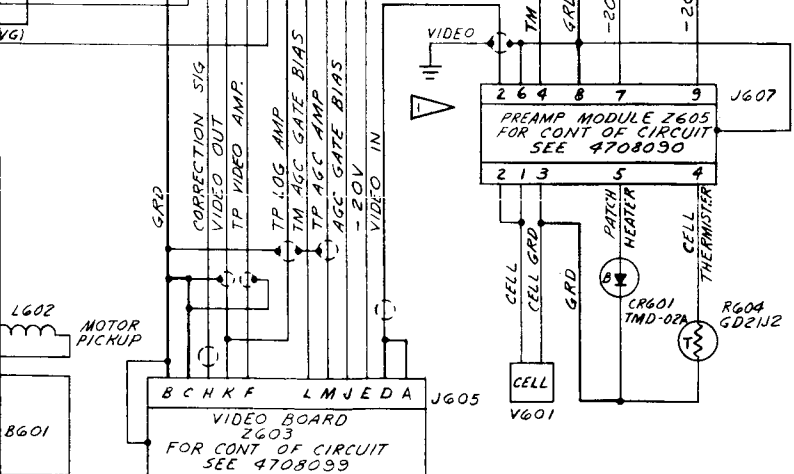
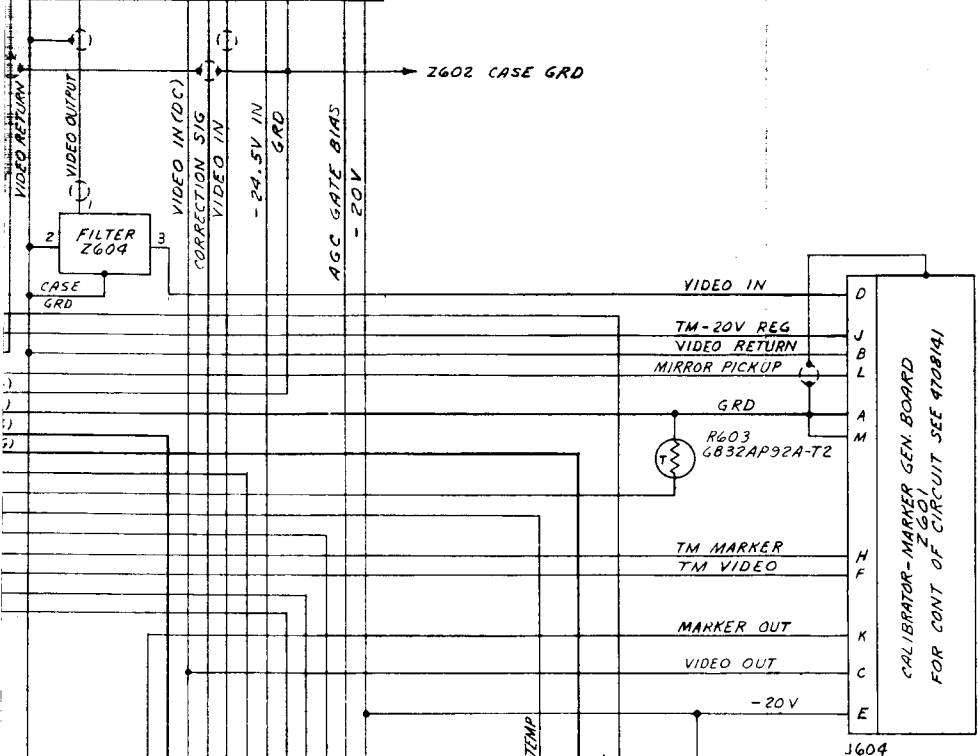


5618015
SERIAL NUMBER

REVISIONS			
TIME	LT#	CHKD BY & DATE	ECN NUMBER

REGULATOR-OUTPUT-AGC BOARD
Z602
FOR CONT OF CIRCUIT SEE 4708133

J D E K H F M A L C J603



4708145

-24.5V RETURN AND PREAMP SHIELD CHASSIS GROUNDED AT PREAMP.

LAST NUMBERS USED

- B601
- CR601
- E605
- J607
- K601
- L602
- P601
- R604
- V601
- Z607

UNLESS OTHERWISE SPECIFIED		MATERIAL
DIMENSIONS ARE TO DIMENSIONS UNLESS OTHERWISE SPECIFIED AND INCLUDE CHEMICALLY APPLIED OR PLATED FINISHES		
TOLERANCES		
BASIC DIMENSIONS	DECIMALS	FRACTIONS
UNDER 1/8	± .01	± .005
1/8 TO 1 INCL	± .01	± .010
OVER 1 IN	± .02	± .015
ANGLES ± .1/32		
CONVENTIONAL TOLERANCES APPLY TO STOCK ITEMS		
SHOP PRACTICE, ESM SECT. 3, APPLIES		

QTY	ITEM	SIZE	PART NUMBER	DESCRIPTION
LIST OF MATERIAL				
INDUSTRIAL LABORATORIES FORT WAYNE, IND.				
A DIVISION OF INTERNATIONAL TELEPHONE AND TELEGRAPH CORPORATION				
WIRING SCHEMATIC, HRIR RADIOMETER (MODIFIED-2)				
SIGNATURE & DATE				
DRAWN				
CHECKED				
DESIGNED				
APPROVED				
SCALE				SHEET D-4708145 SHEET

2

APPENDIX II

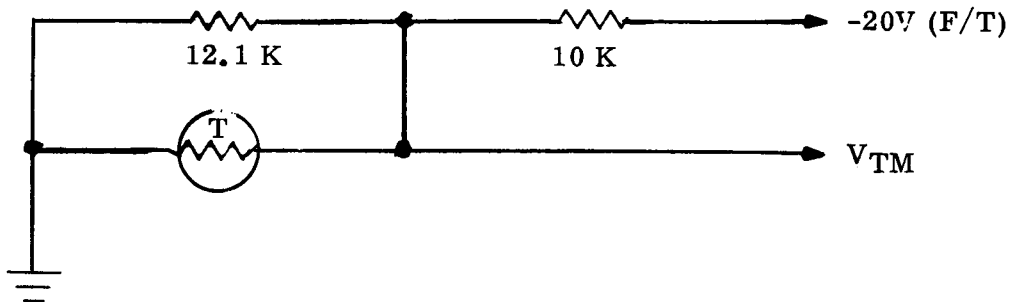
TELEMETRY COMPENDIUM

Several requirements are common to all points:

1. All TM voltages are in the range 0 to -6.35 volts as required.
2. All points are analog functions.
3. The basic 16 second sampling rate is adequate for all points.
4. The PCM conversion accuracy of 1 count = 50 mv is adequate.

Reference "A" Temperature (J602-1)

Measures the temperature of the portion of the radiometer housing used to provide a black body reference calibration during the back-scan.



Impedance: See curve

Voltage: See curve (active day and night)

Failure Modes: TM open - no effect

TM Shorts - Continuous 2 ma power drain

Thermistor open - 10.8 volts at TM output

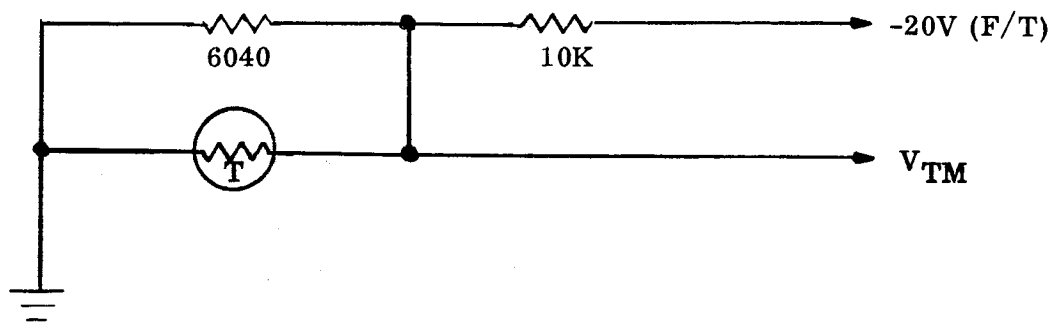
Thermistor shorts - zero TM volts, 2 ma power drain

Reference "B" Temperature (J602-9)

Same as Reference "A". Provide redundancy and temperature gradient indication.

Electronic Housing Temperature (Reference E) (J602-2)

Measures the temperature of the electronics module.



Impedance: See curve

Voltage: See curve (active day and night)

Failure Modes: TM open - no effect

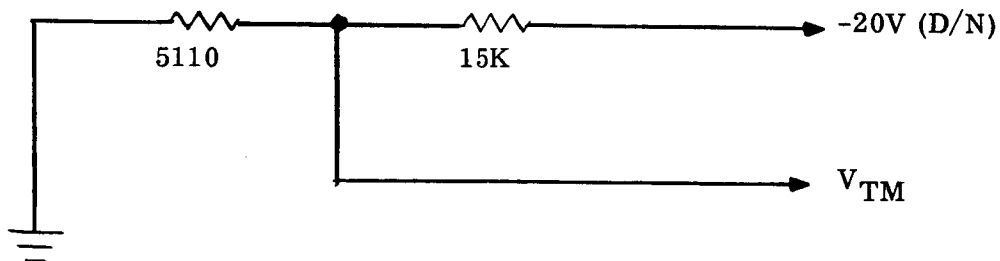
TM Shorts - Continuous 2 ma power drain

Thermistor open - 7.5 volts at TM output

Thermistor shorts - zero TM volts, 2 ma power drain

-20 Volt Regulator (J602-11)

Measures the output of the -20 volt regulator used for driving all electronics circuitry (except telemetry).



Impedance: 3.8 K

Voltage: Normally 5.1 volts \pm 0.5 volts (night), zero volts (day)

Failure Modes: TM open - no effect; TM shorts - continuous 1.33 ma power drain

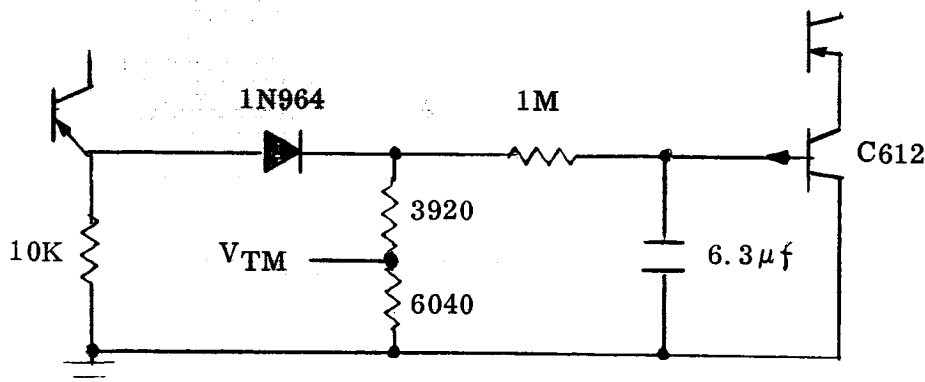
-20 Volts Full Time (J602-14)

Measures the output of the -20 volt regulator used for driving the telemetry functions and cell temperature control.

Same circuit and parameters as -20 volt regulator.

AGC Gate Bias (J602-15)

Provides an indication of the magnitude of injected radiation bias correction signal. Actually reads the voltage applied to the gate electrode of the AGC transistor.



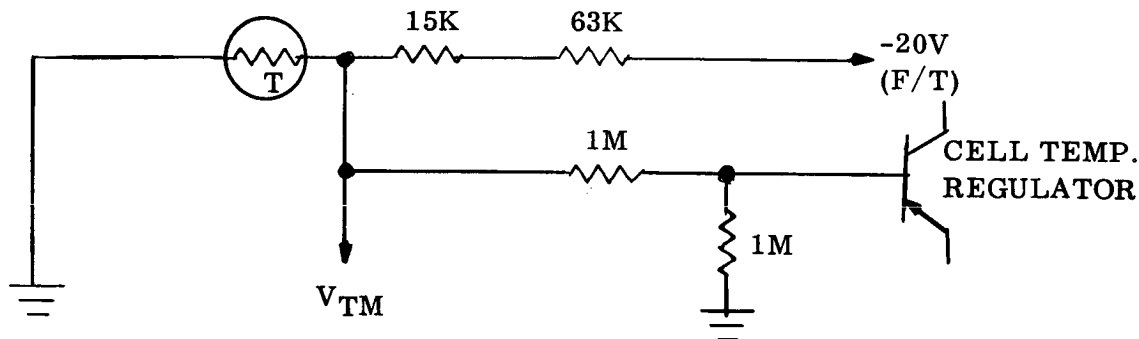
Impedance: Nominally 6K

Voltage: See curve (active night only)

Failure Modes: TM open - no effect; TM shorts - zero TM volts

Cell Temperature (J602-10)

Measures the temperature of the radiating patch which is used for cooling the detector cell. Normal range of temperatures at this point is -70 to -80 degrees centigrade. The patch (and cell) temperature is automatically regulated.



Impedance: See curve

Voltage: See curve (active day and night)

Failure Modes: TM open - no effect

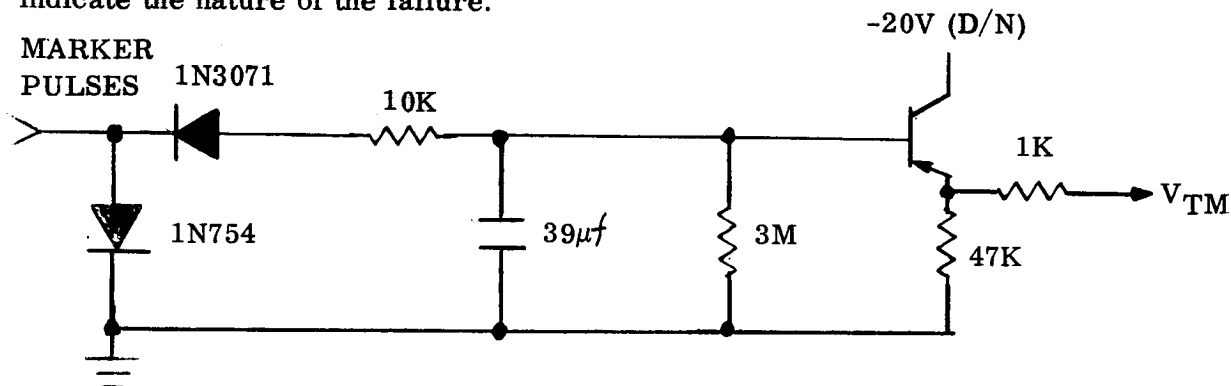
TM shorts - Loss of temperature control. Cell will cool to maximum level.

Thermistor opens - Loss of temperature control. Cell will not be allowed to cool.

Thermistor shorts - Same as TM shorts.

Marker Pulse (J602-4)

Seven pulses of 6 msec duration are generated each revolution of the scanning mirror. The presence of this signal indicates mirror rotation and marker generation. Absence indicates either motor or pulse generator failure. The seven pulses are fed to an integrating circuit having a time constant of 300 seconds, allowing an output voltage near -4 volts. If this signal falls below 2 volts, it is an indication of either the motor slowing down or pulse amplitude decreasing. Correlation of this signal with the sync pulse received from the recorder and the motor TM signal will indicate the nature of the failure.



Impedance: 47 K

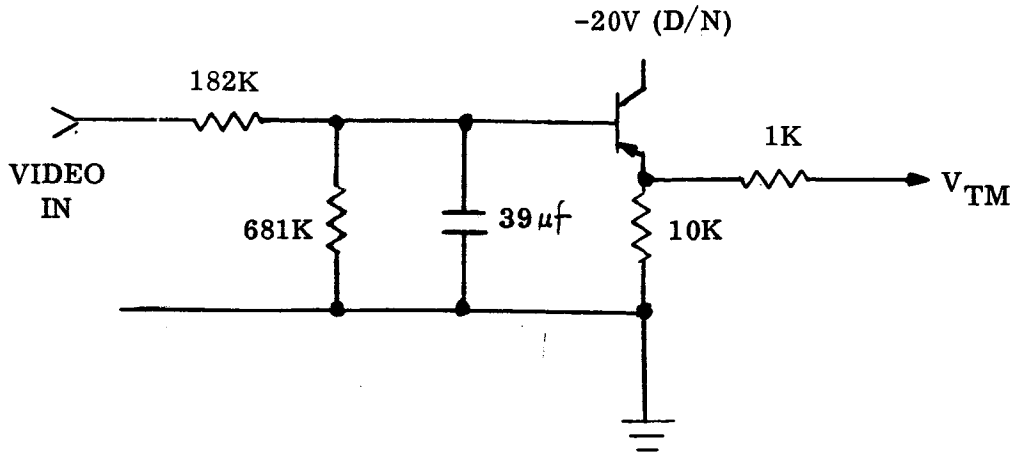
Voltage: Nominally 4 volts (night), zero volts (day)

Failure Modes: TM open - no effect

TM Shorts - Transistor current increases to 20 ma (Max.)
Marker pulses unaffected

Video Output (J602-12)

The video signal as present at the output of the radiometer is fed to a long time-constant network where it is averaged, then applied to an emitter follower to reduce the output impedance. Since the video signal will vary from 0 to -6 volts during each scan interval, and the level will be determined by the temperature of the scene being viewed, it is impossible to predict the exact conditions at all times. The following limits are anticipated, assuming at least one look at outer space and one look at the reference surface of the radiometer. The maximum average signal will not exceed -3 volts, the minimum should not be less than -0.5 volts, and will vary between these limits depending on the average conditions of the earth in the field-of-view. A time constant of approximately 10 seconds will maintain the output voltage to within 10 percent of the average value.



Impedance: 10 K

Voltage: See text (night only), zero volts (day)

Failure Modes: TM open - no effect

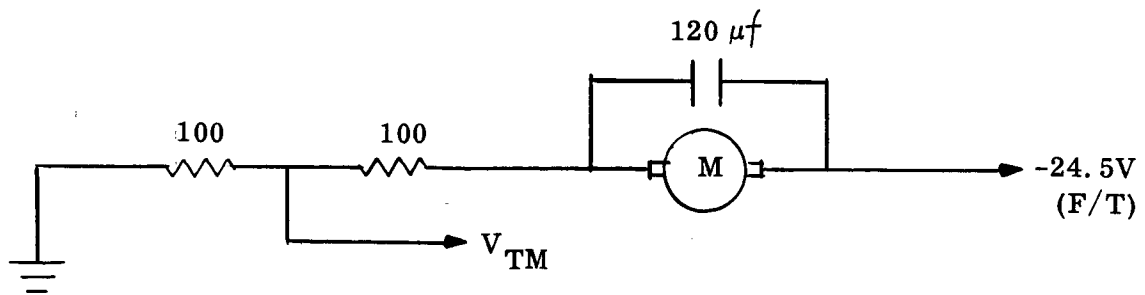
TM shorts - Transistor current increases to 20 ma (Max.)
Video signal unaffected.

Motor Rotation (J602-13)

Indicates one of three possible conditions with respect to the drive motor:

1. Motor synchronous
2. Motor stalled
3. Motor off

By measuring the voltage dropped across a portion of the series motor resistor, a measure of motor current and power is obtained. During synchronous rotation the output will be approximately -3 volts. Should the motor stall, the current will increase causing the output to increase to approximately -4 volts. When the motor is off, the output will read zero volts.

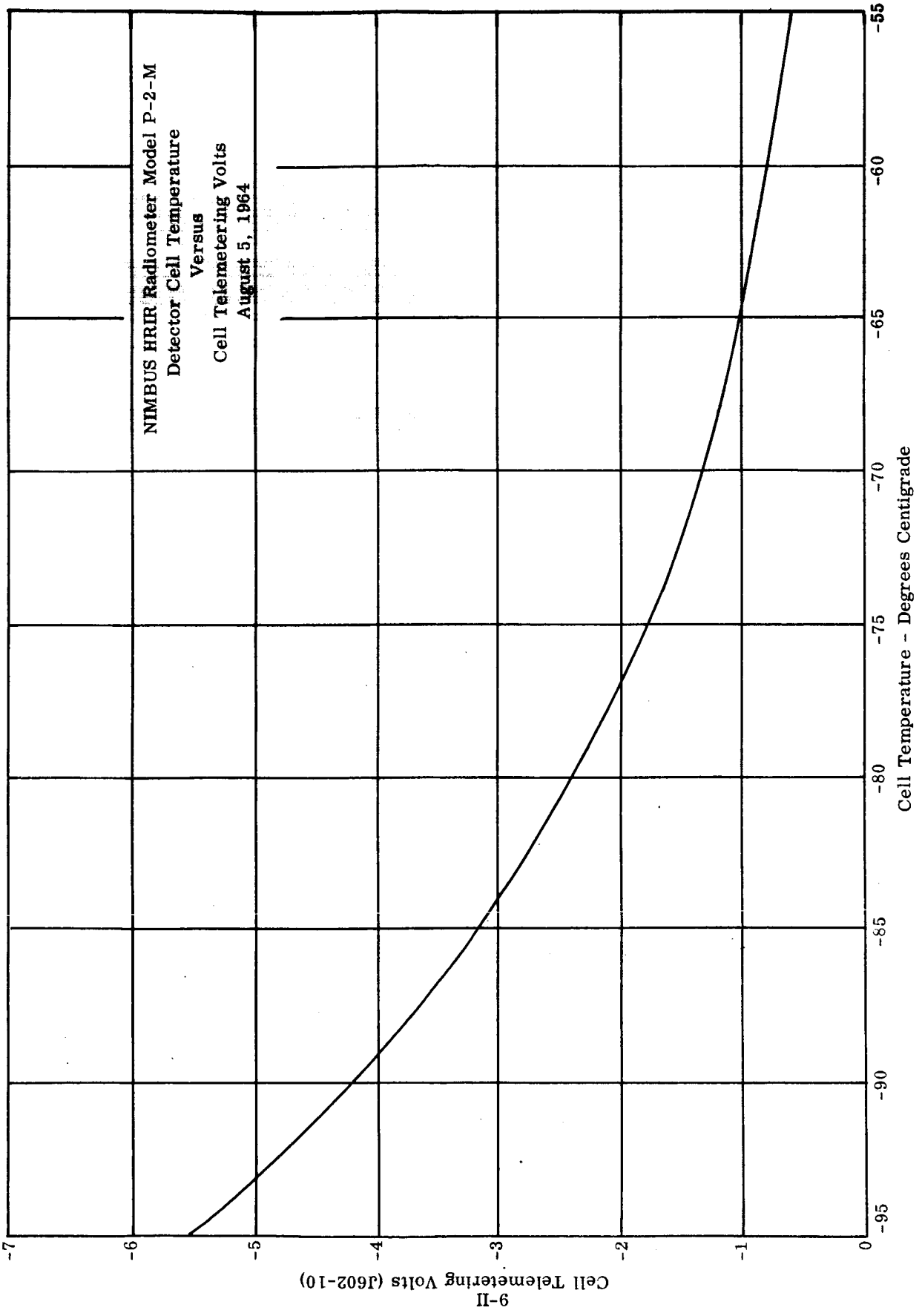


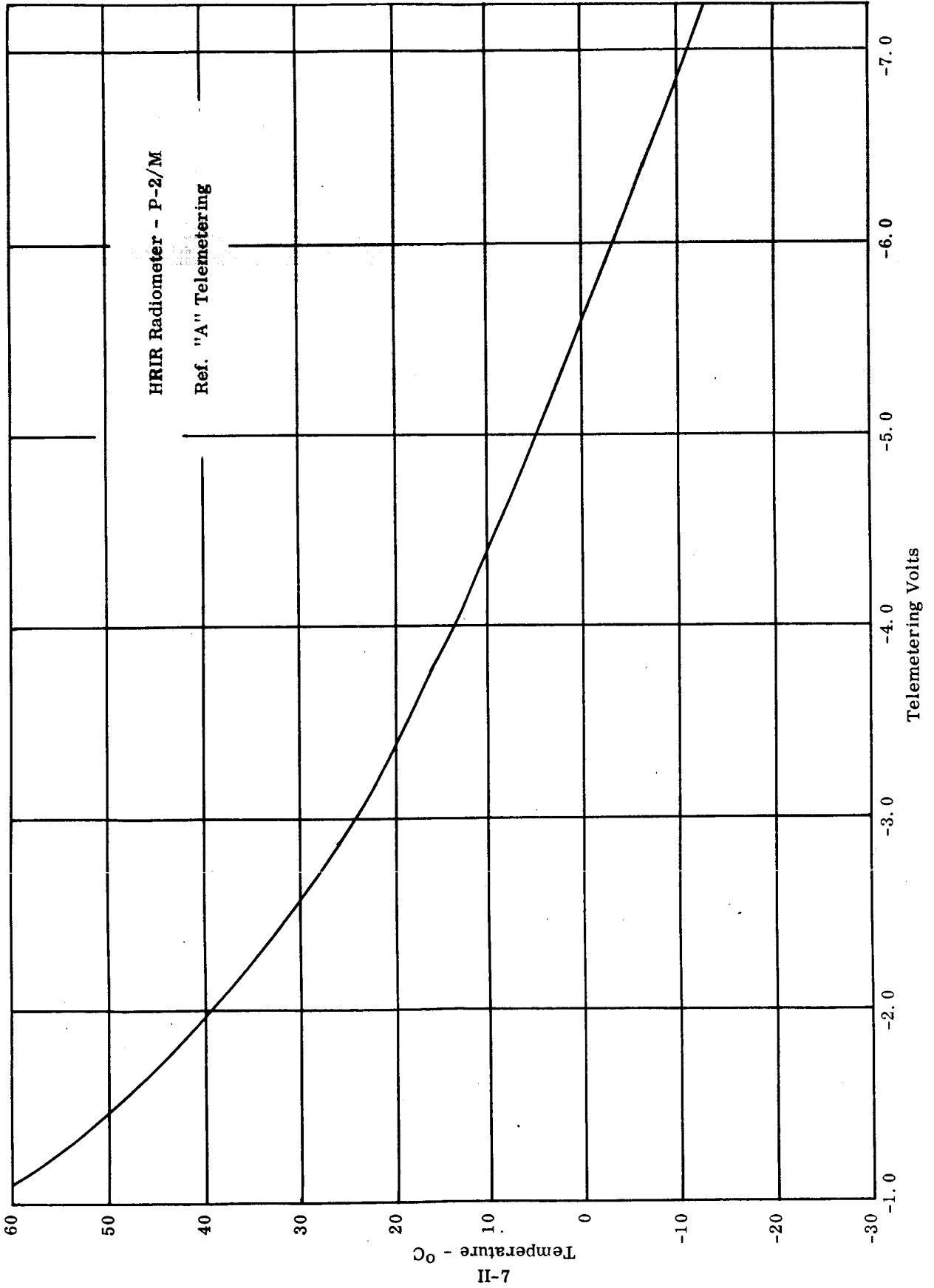
Impedance: 100 ohms

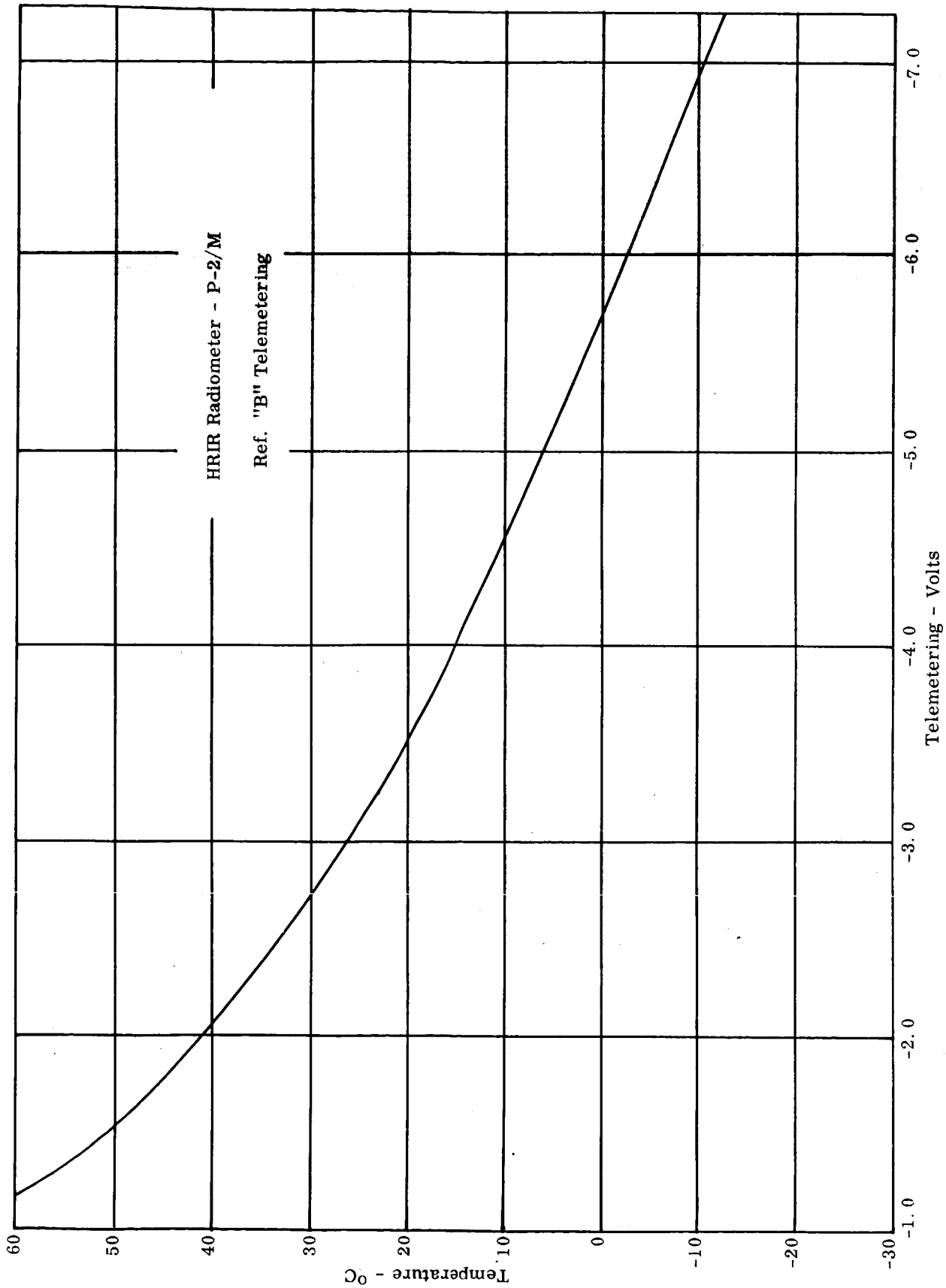
Voltage: See text

Failure Modes: TM open - no effect

TM shorts - reduced motor efficiency

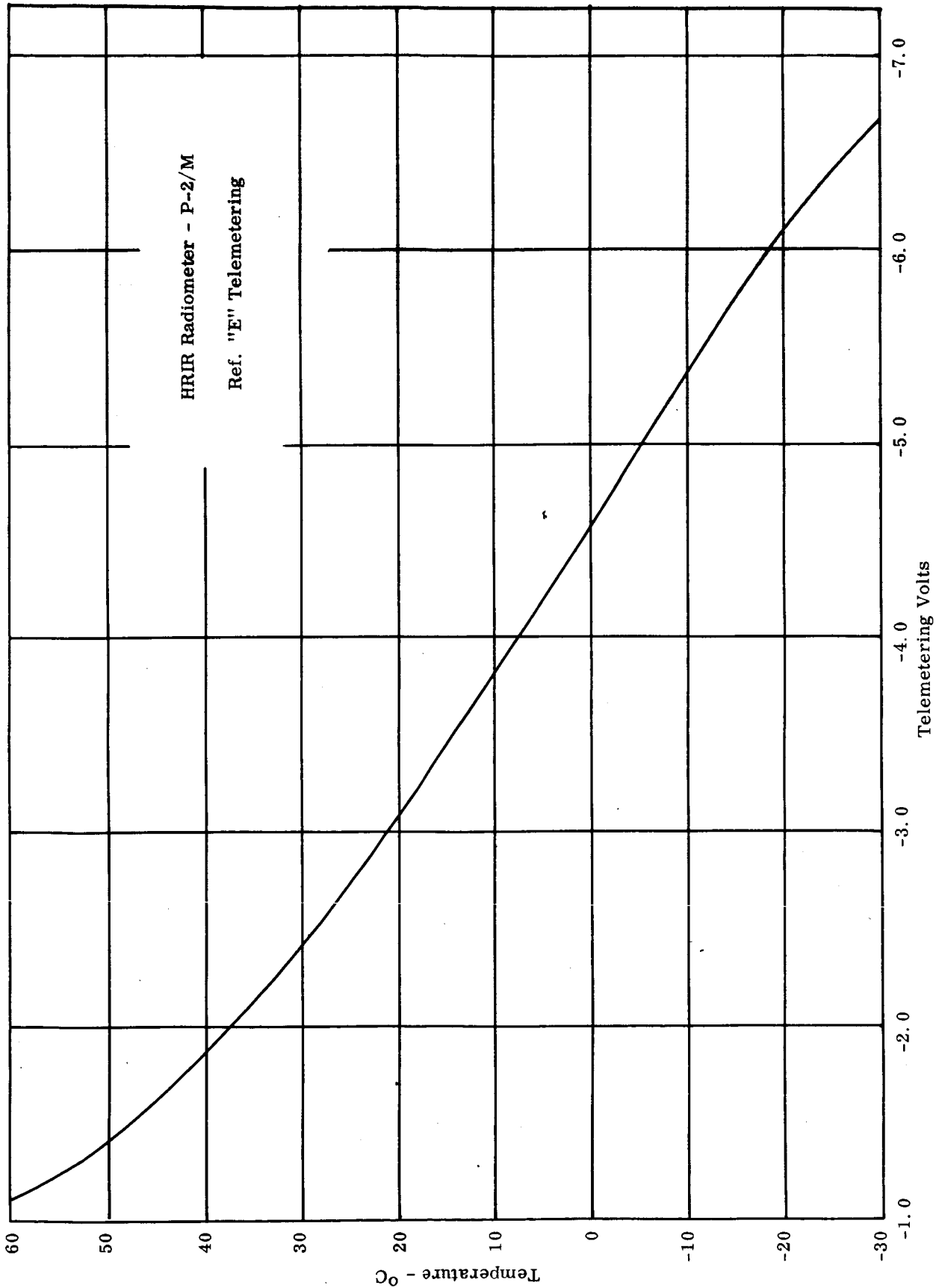


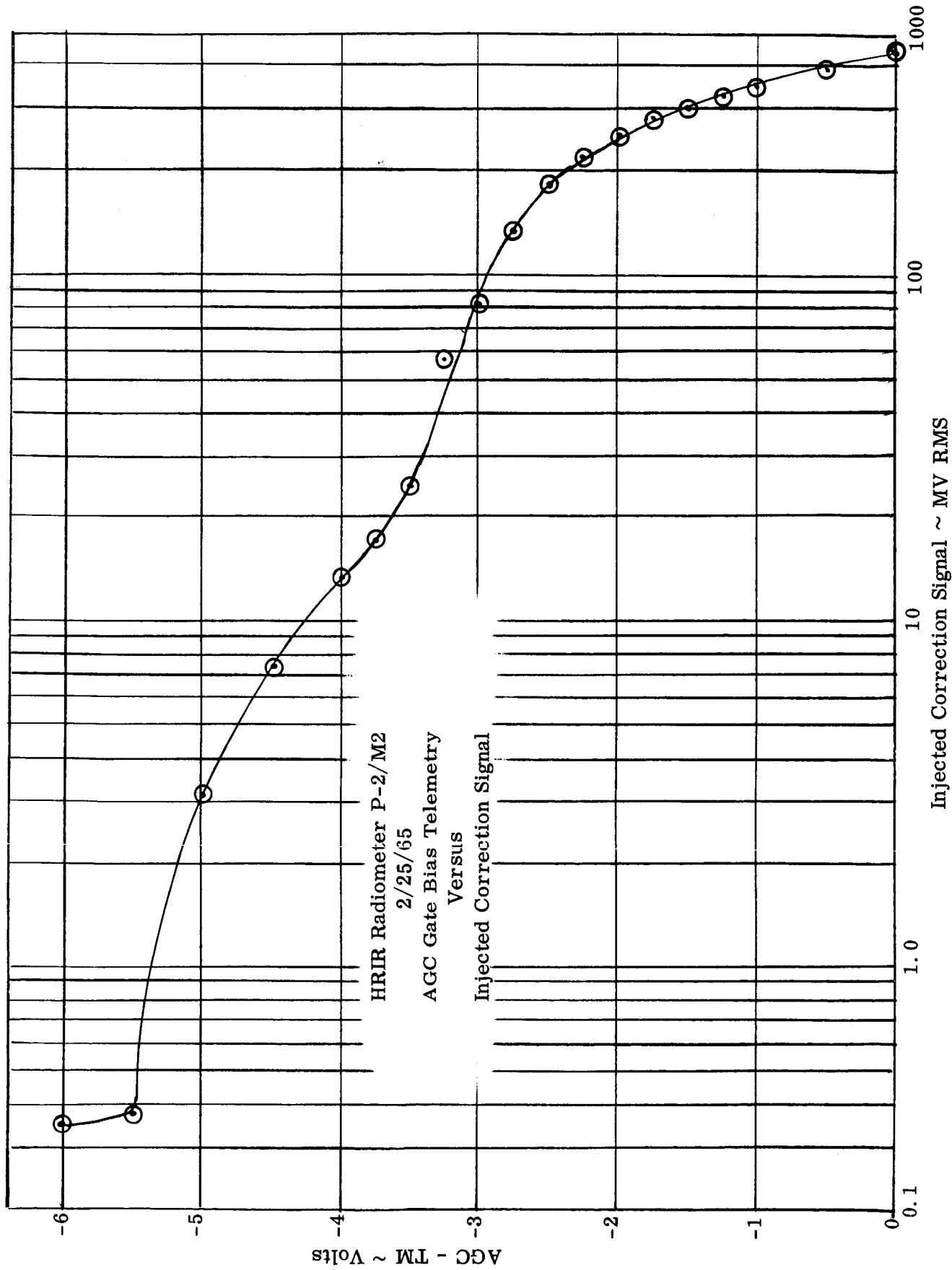




HRIR Radiometer - P-2/M

Ref. "B" Telemetering





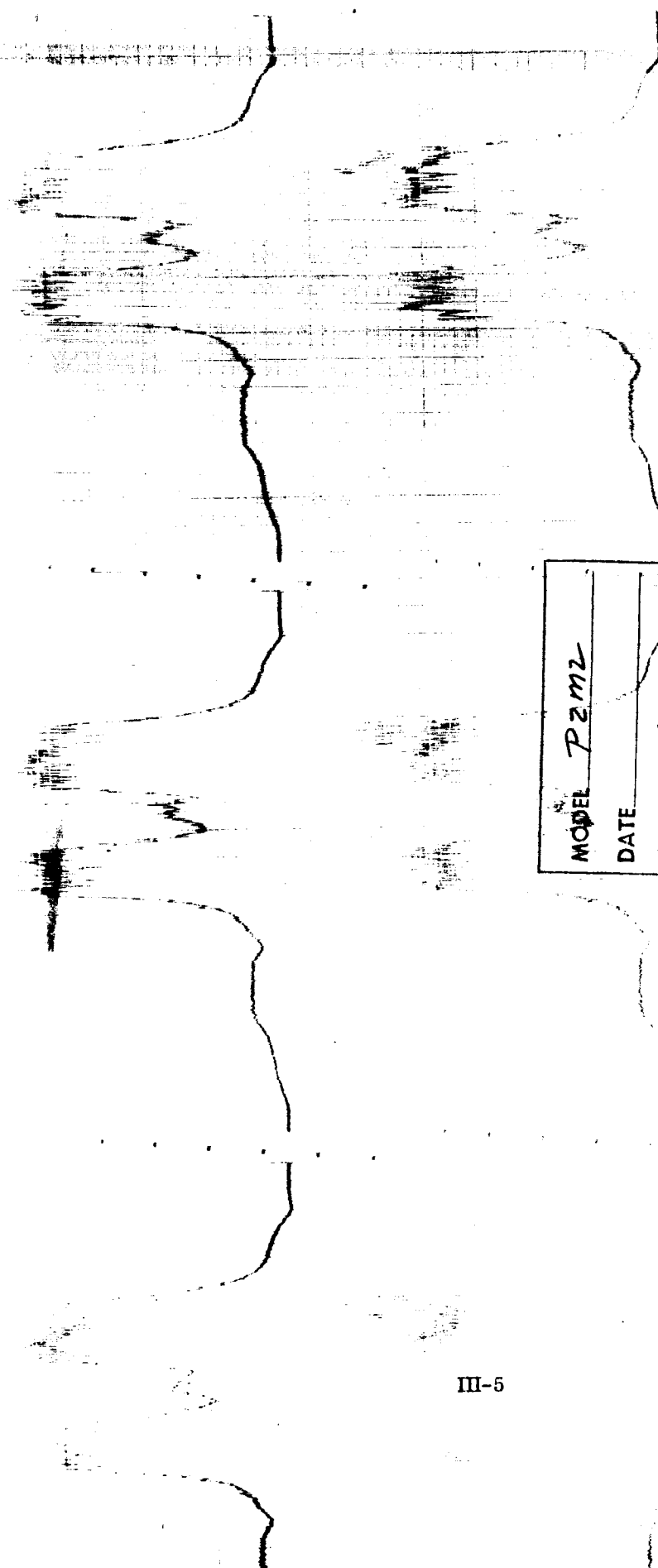
APPENDIX III

CALIBRATION VISICORDER CHARTS

MODEL	P2M2
DATE	
TARGET	190 °K
SATELLITE	+50 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2M2</u>
DATE	_____
TARGET	<u>200</u> °K
SATELLITE	<u>750</u> °C
PRESSURE	_____
INITIAL	_____
FINAL	<u>✓</u>

MODEL	P2m2
DATE	
TARGET	210 °K
SATELLITE	+50 °C
PRESSURE	
INITIAL	FINAL ✓

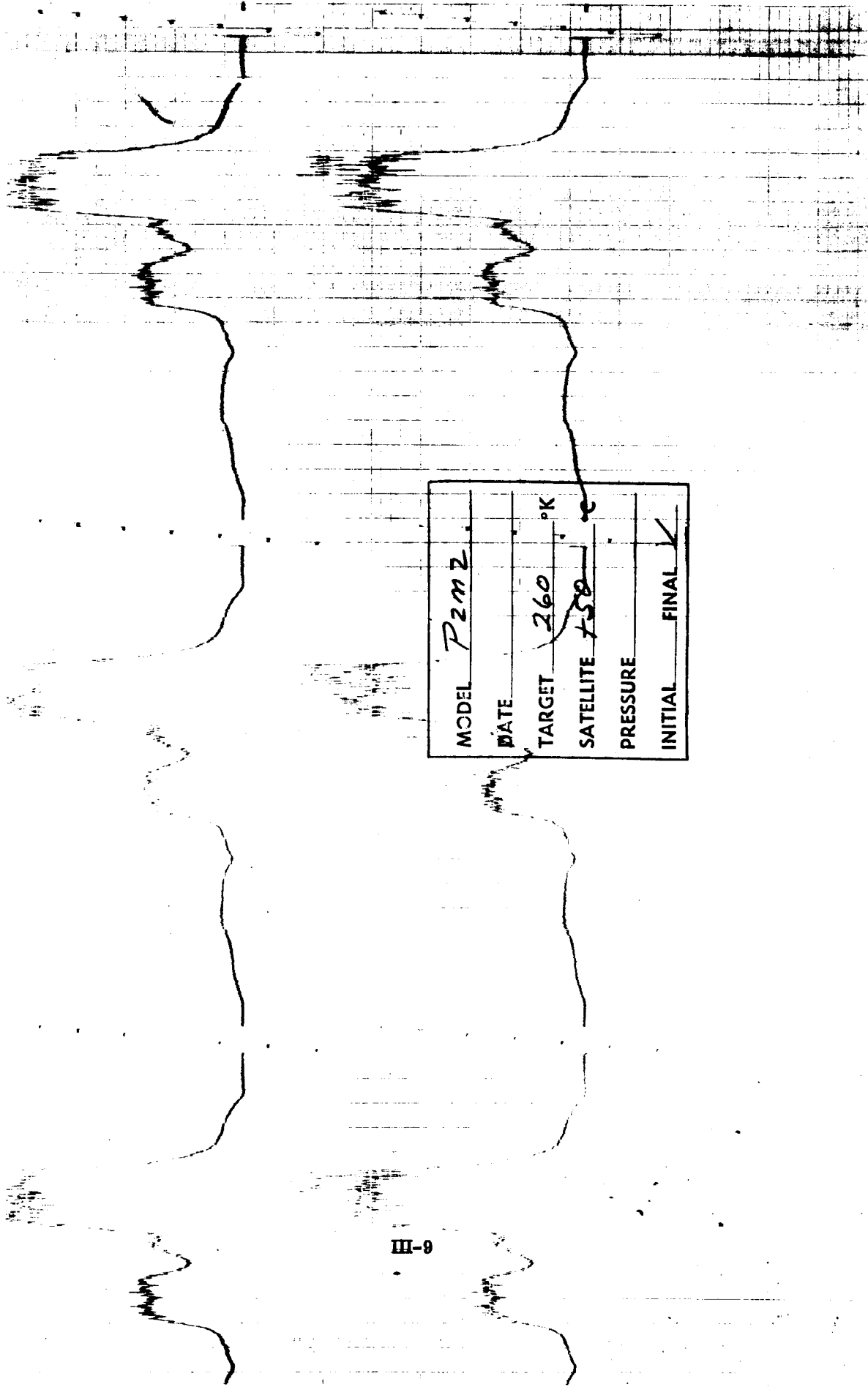


MODEL	P2M2
DATE	
TARGET	220 °K
SATELLITE	750 °C
PRESSURE	
INITIAL	FINAL ✓

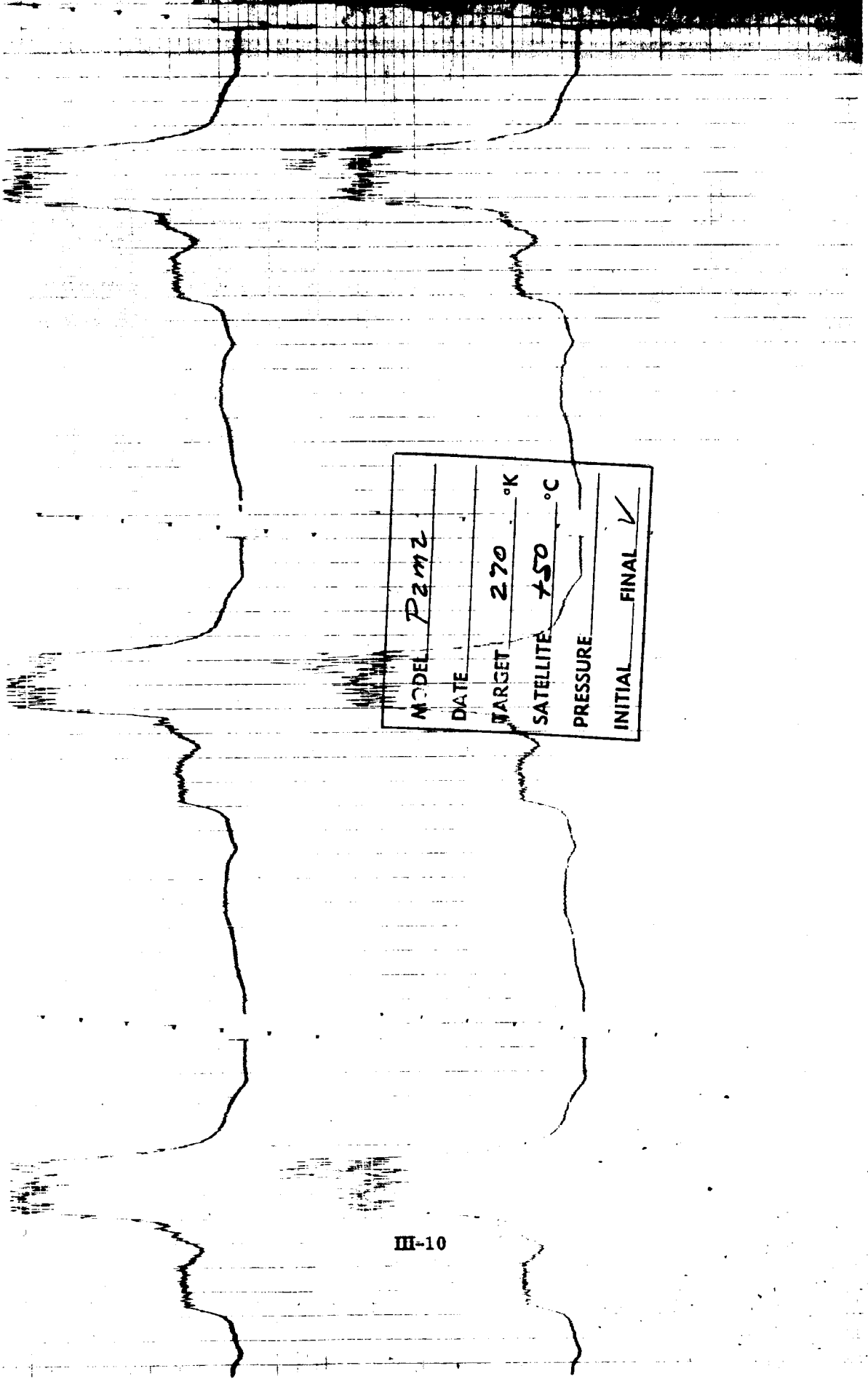
MODEL	P2M2
DATE	
TARGET	230 °K
SATELLITE	+50 °C
PRESSURE	
INITIAL	FINAL

MODEL	Pemz
DATE	
TARGET	240 °K
SATELLITE	750 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2m2</u>
DATE	
TARGET	<u>250</u> °K
SATELLITE	<u>450</u> °C
PRESSURE	
INITIAL	
FINAL	<u>✓</u>



MODEL	P2M2
DATE	
TARGET	260 °K
SATELLITE	758 °C
PRESSURE	
INITIAL	FINAL ✓



MODEL	P2mz
DATE	
TARGET	270 °K
SATELLITE	750 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P 2 M 2
DATE	
TARGET	280 °K
SATELLITE	750 °C
PRESSURE	
INITIAL	FINAL
	✓

MODEL	P2m2
DATE	
TARGET	290 °K
SATELLITE	150 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	500 °K
SATELLITE	ASD °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	310 °K
SATELLITE	150 °C
PRESSURE	
INITIAL	FINAL
	✓

MODE	P2M2
DATE	
TARGET	320 °K
SATELLITE	450 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL PM12

DATE

TARGET 330 °K

SATELLITE 750 °C

PRESSURE

INITIAL FINAL ✓

MODEL	P2M2
DATE	
TARGET	340 °K
SATELLITE	750 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	190 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	200
SATELLITE	+45
PRESSURE	
INITIAL	FINAL ✓

HL-13

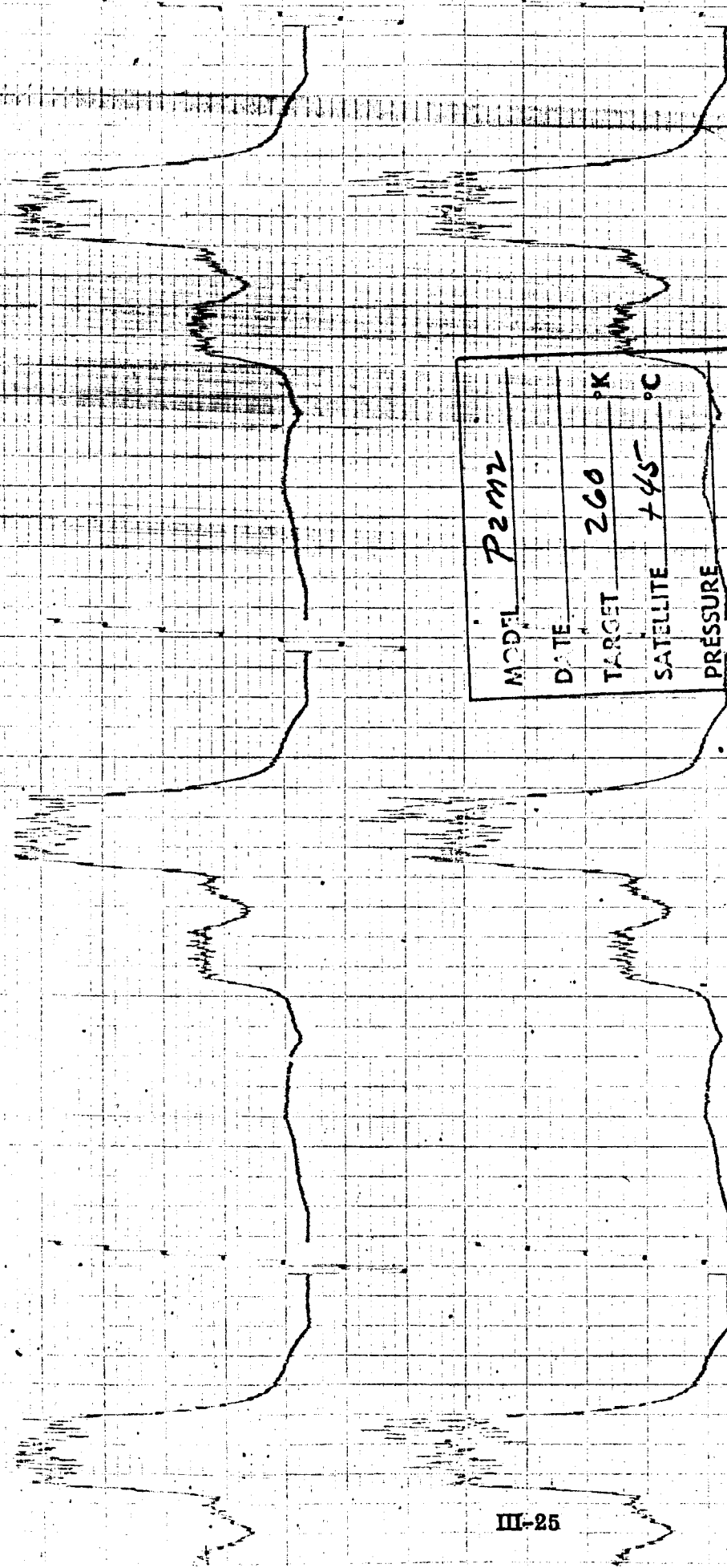
MODEL	P2M2
DATE	
TARGET	210 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	220 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

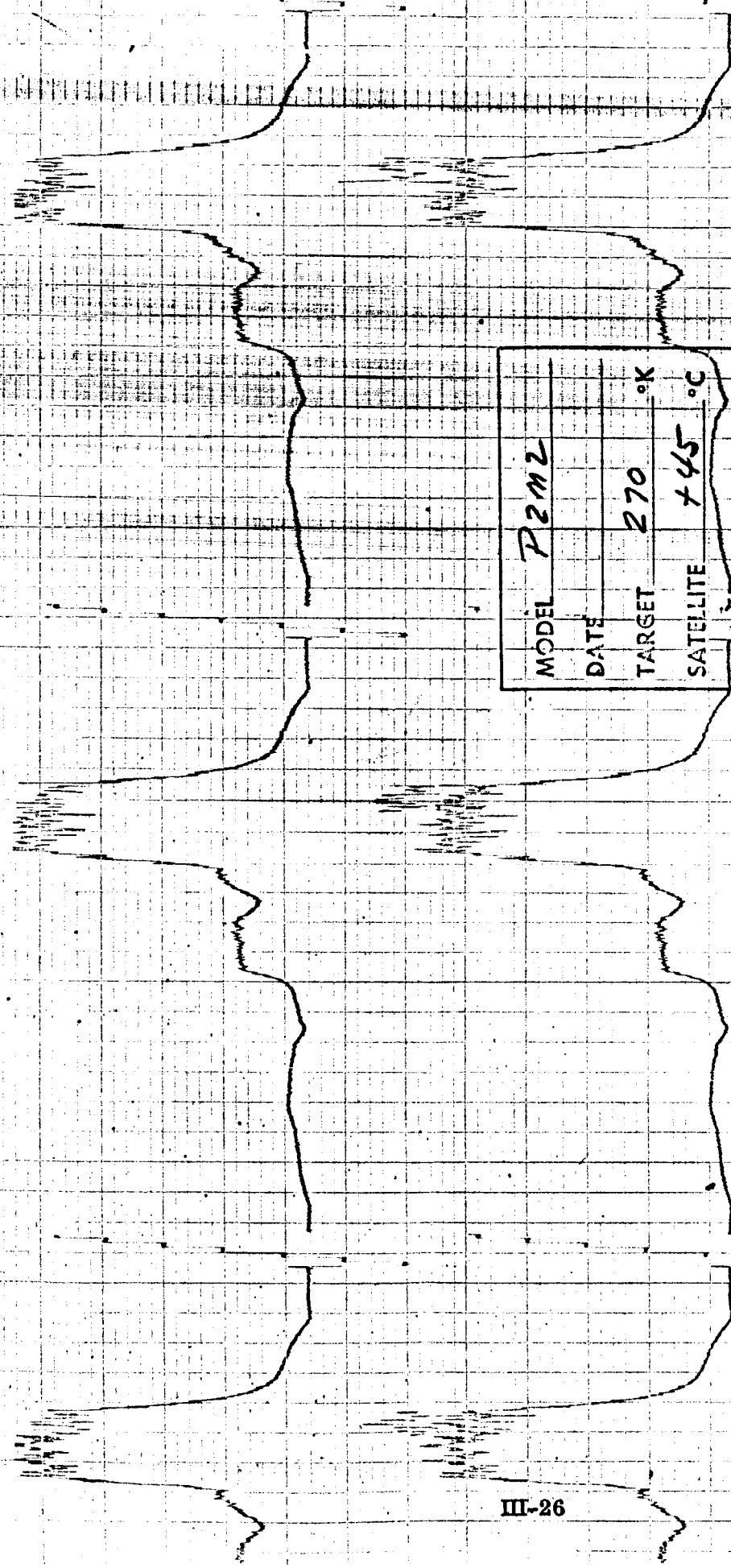
MODEL	P 2M2
DATE	
TARGET	230 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	-
TARGET	240 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	250 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓



MODEL	P2M2		
DATE			
TARGET	260	°K	
SATELLITE	+45	°C	
PRESSURE			
INITIAL			
			FINAL <input checked="" type="checkbox"/>



MODEL	P2M2
DATE	
TARGET	270 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	280 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2		
DATE			
TARGET	290	°K	
SATELLITE	+45	°C	
PRESSURE			
INITIAL	FINAL	<input checked="" type="checkbox"/>	

MODEL	P2M2
DATE	
TARGET	300 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL <input checked="" type="checkbox"/>

MODEL	P2M2
DATE	
TARGET	310 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL

MODEL	P2M2
DATE	
TARGET	320 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	330 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	340 °K
SATELLITE	+45 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2m2
DATE	
TARGET	190 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	200 °K
SATELLITE	± 25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	210 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	220 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

III-38

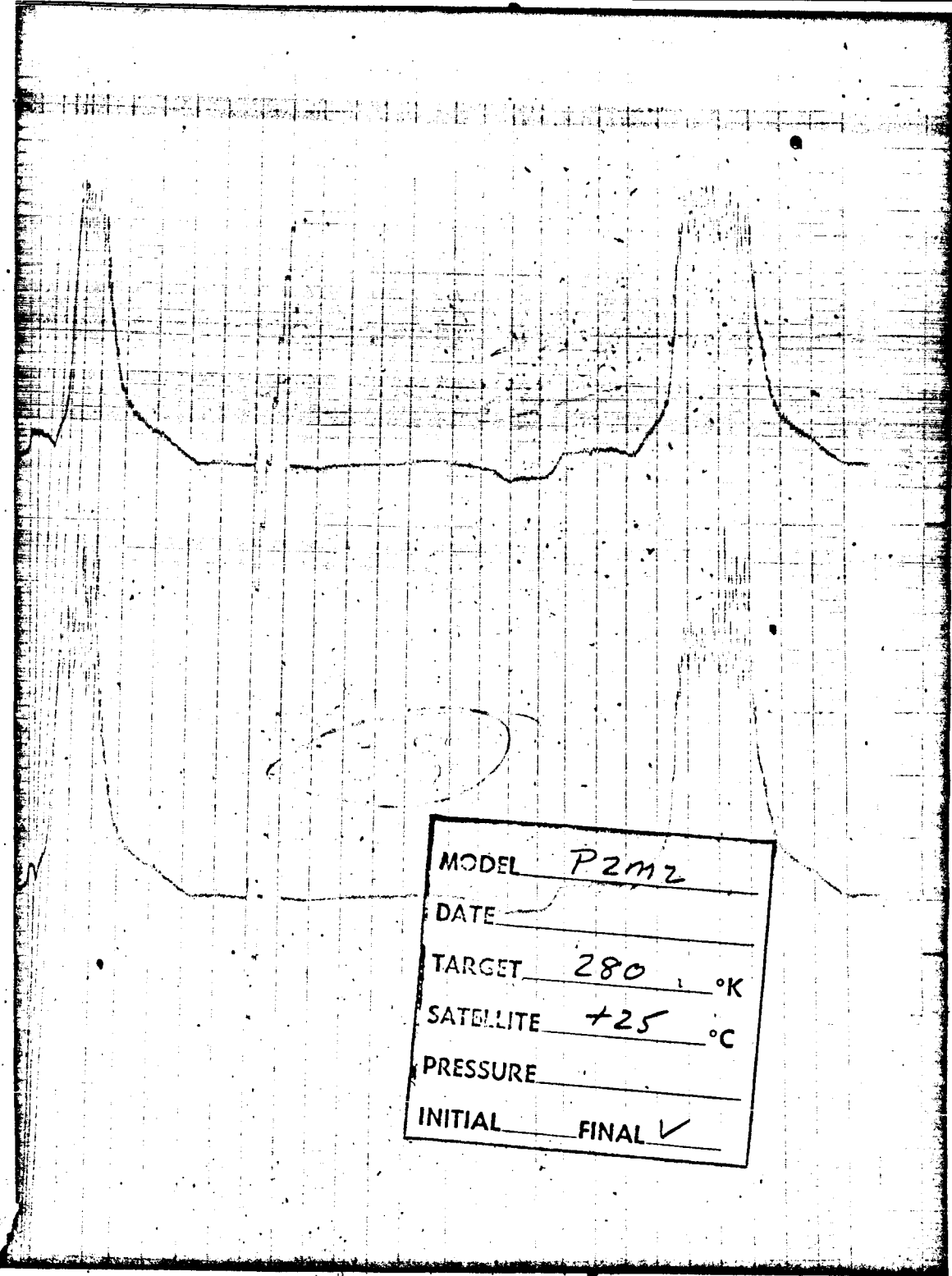
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DATE	
TARGET	230 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	240 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	250 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	PZM2
DATE	
TARGET	260 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2m2
DATE	
TARGET	270 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓



MODEL	P2M2
DATE	
TARGET	280 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	290 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2m12
DATE	
TARGET	300 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	310 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	320 °K
SATELLITE	+25 °C
PRESSURE	
INITIAL	FINAL <input checked="" type="checkbox"/>

MODEL	P2M2
DATE	
TARGET	330 °K
SATELLITE	725 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>PZM2</u>
DATE	<u> </u>
TARGET	<u>340</u> °K
SATELLITE	<u>+25</u> °C
PRESSURE	<u> </u>
INITIAL	<u> </u>
FINAL	<u>✓</u>

MODEL	P2M2
DATE	
TARGET	190 °K
SATELLITE	75 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2MV
DATE	
TARGET	200 °K
SATELLITE	+5 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2M7</u>
DATE	
TARGET	<u>270</u> °K
SATELLITE	<u>+5</u> °C
PRESSURE	
INITIAL	
FINAL	<input checked="" type="checkbox"/>

MODEL	<u>P2M2</u>
DATE	<u> </u>
TARGET	<u>220</u> °K
SATELLITE	<u>75</u> °C
PRESSURE	<u> </u>
INITIAL	<u> </u>
	FINAL <input checked="" type="checkbox"/>

MODEL	P2M2
DATE	
TARGET	230 °K
SATELLITE	+5 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2M2</u>
DATE	
TARGET	<u>240</u> °K
SATELLITE	<u>+5</u> °C
PRESSURE	
INITIAL	
FINAL	<u>✓</u>

MODEL	<u>P2M2</u>
DATE	
TARGET	<u>250</u> °K
SATELLITE	<u>+5</u> °C
PRESSURE	
INITIAL	<u>FINAL</u> ✓

MODEL	P2M2
DATE	
TARGET	260 °K
SATELLITE	75 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	270 °K
SATELLITE	+5 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2		
DATE			
TARGET	280	°K	
SATELLITE	+5	°C	
PRESSURE			
INITIAL		FINAL	✓

MODEL	P2M2
DATE	
TARGET	290 °K
SATELLITE	75 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2m2
DATE	
TARGET	300 °K
SATELLITE	+5 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	Pzmz
DATE	
TARGET	310 °K
SATELLITE	+75 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	320 °K
SATELLITE	75 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2m2	
DATE		
TARGET	330	°K
SATELLITE	+5	°C
PRESSURE		
INITIAL	FINAL	✓

MODEL	P2M2
DATE	
TARGET	340 °K
SATELLITE	±5 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2M2</u>
DATE	<u> </u>
TARGET	<u>190</u> °K
SATELLITE	<u>0</u> °C
PRESSURE	<u> </u>
INITIAL	<u> </u>
FINAL	<u> </u> ✓

MODEL	<u>PZMZ</u>
DATE	_____
TARGET	<u>200</u> °K
SATELLITE	<u>0</u> °C
PRESSURE	_____
INITIAL	_____
	FINAL <input checked="" type="checkbox"/>

MODEL	P2M2
DATE	
TARGET	210 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2M2</u>
DATE	<u> </u>
TARGET	<u>220</u> °K
SATELLITE	<u>0</u> °C
PRESSURE	<u> </u>
INITIAL	<u> </u>
FINAL	<u> </u> ✓

MODEL	P2M2
DATE	
TARGET	230 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	240 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	250 °K
SATELLITE	0 °C
PRESSURE	✓
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	260 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2m2
DATE	
TARGET	270 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	P2M2
DATE	
TARGET	280 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2M2</u>
DATE	
TARGET	<u>290</u> °K
SATELLITE	<u>0</u> °C
PRESSURE	
INITIAL	<u>FINAL</u> ✓

MODEL	<u>P2m2</u>
DATE	_____
TARGET	<u>300</u> °K
SATELLITE	<u>0</u> °C
PRESSURE	_____
INITIAL	_____
FINAL	<u>✓</u>

MODEL	P2M2
DATE	
TARGET	310 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL ✓

MODEL	<u>P2mz</u>
DATE	_____
TARGET	<u>320</u> °K
SATELLITE	<u>0</u> °C
PRESSURE	_____
INITIAL	<u>FINAL</u> ✓

MODEL	P2M2
DATE	
TARGET	330 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL <input checked="" type="checkbox"/>

MODEL	P2M2
DATE	
TARGET	340 °K
SATELLITE	0 °C
PRESSURE	
INITIAL	FINAL <input checked="" type="checkbox"/>

APPENDIX IV

CONNECTOR PIN DESIGNATIONS

1. Connector J-601, Power and Signal

Type: DA 15P, Male, 15 Contact

Recommended Mating Connector: DA 15S with Cannon 20419
Screw Lock

<u>Contact</u>	<u>Purpose</u>
1	Marker pulse output
2	Video output
3	No connection
4	Video signal return
5	Chassis ground
6	Motor sync, phase 1
7	Relay control, Off
8	Relay control, On
9	No connection
10	No connection
11	-24.5 Volt to electronics (day/night)
12	System ground
13	Motor sync, phase 2, lagging phase 1
14	-24.5 Volt supply (full time)
15	Relay control common

2. Connector J-602 Telemetry

Type: DA 15S, Female, 15 Contact

Recommended Mating Connector: DA 15P with Cannon 20419
Screw Lock

<u>Contact</u>	<u>Purpose</u>
1	Telemetry, reference surface temperature A (Ref. "A")
2	Telemetry, electronic housing temperature (Ref. "E")
3	Test Point No. 4 (AGC output)
4	Telemetry, marker pulse
5	Test Point No. 1* (Video Amp Output)
6	Test Point No. 2* (Ref. Sig. Output)
7	Test Point No. 3* (Log Amp Output)
8	System Ground
9	Telemetry, reference surface temp. B (Ref. "B")
10	Telemetry, detector cell temperature
11	Telemetry, -20 Volt regulator
12	Telemetry, video output
13	Telemetry, mirror rotation
14	Telemetry, -20 volt supply (full time)
15	Telemetry, AGC Gate bias

APPENDIX V

DETECTOR CELL DATA

Serial No.	H75B4
Bias Voltage	6 volts
Load Resistance	2.5 Megohms
Frequency	1470 cps
Measured Signal	225 mv
Measured Noise	1.1 mv
Source Temperature	500 degrees K
Calculated 3.4 to 4.2 Micron D*	2.72×10^{10} cm cps ^{1/2} /watt

APPENDIX VI
FIELD EFFECT TRANSISTOR DATA

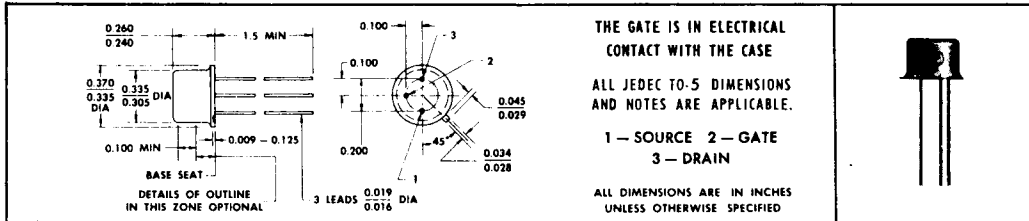
TYPES 2N2497, 2N2498, 2N2499, 2N2500 P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS



FOR SMALL-SIGNAL, LOW-NOISE APPLICATIONS

- Guaranteed 10 cps Noise Figure (2N2500)
- High Input Impedance (>5 megohms at 1 kc)
- High Nuclear Radiation-Damage Resistance

*mechanical data



*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Gate Current	10 ma
Total Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 1)	0.5 w
Total Device Dissipation at (or below) 25°C Case Temperature (See Note 2)	1.5 w
Storage Temperature Range	-195°C to +300°C

*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N2497		2N2498		2N2499		2N2500		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
BV_{DGO} Drain-Gate Breakdown Voltage (See Note 3)	$I_D = -10 \mu A, I_S = 0$	-20		-20		-20		-20		v
I_{GSS} Gate Cutoff Current	$V_{GS} = 10 v, V_{DS} = 0$	0.01		0.01		0.01		0.01		μA
I_{GSS} Gate Cutoff Current	$V_{GS} = 10 v, V_{DS} = 0, T_A = 150^\circ C$	10		10		10		10		μA
$I_{D(on)}$ Zero-Gate-Voltage Drain Current	$V_{DS} = -10 v, V_{GS} = 0$	-1	-3	-2	-6	-5	-15	-1	-6	ma
$I_{D(off)}$ Pinch-Off Drain Current	$V_{DS} = -15 v, V_{GS}$ (See Note 4)	-10		-10		-10		-10		μA
r_{DS} Static Drain-Source Resistance	$I_D = -100 \mu A, V_{GS} = 0$	1000		800		600				ohm
$ y_{is} $ Small-Signal Common-Source Input Admittance	$V_{DS} = -10 v, I_D$ (See Note 5) $f = 1 kc$	0.2		0.2		0.2		0.2		μmho
$ y_{fs} $ Small-Signal Common-Source Forward Transfer Admittance		1000	2000	1500	3000	2000	4000	1000	2200	μmho
$ y_{rs} $ Small-Signal Common-Source Reverse Transfer Admittance		0.1		0.1		0.1		0.1		μmho
$ y_{os} $ Small-Signal Common-Source Output Admittance		20		40		100		20		μmho
$ y_{fs} $ Small-Signal Common-Source Forward Transfer Admittance	$V_{DS} = -10 v, I_D$ (See Note 5) $f = 10 mc$	900		1350		1800		900		μmho
C_{iss} Common-Source Short-Circuit Input Capacitance	$V_{GS} = 0, V_{DS} = -10 v, f = 140 kc$	32		32		32		32		pf

*operating characteristics at 25°C free-air temperature

NF	Spot Noise Figure	$V_{DS} = -5 v, I_D = -1 ma, f = 1 kc, R_G = 1 MS\Omega$				
		$V_{DS} = -5 v, I_D = -1 ma, f = 10 cps, R_G = 10 MS\Omega$	3	3	4	1
					5 db	

- NOTES: 1. Derate linearly to 175°C free-air temperature at the rate of 3.3 mw/C°.
 2. Derate linearly to 175°C case temperature at the rate of 10 mw/C°.
 3. This parameter corresponds closely to BV_{DSS} (the Drain-Source Breakdown Voltage for $V_{GS} = 0$). BV_{DSX} (the Drain-Source Breakdown Voltage for other values of V_{GS}) may be calculated from:
 $|BV_{DSX}| \cong |BV_{DGO}| - |V_{GS}|$

	2N2497	2N2498	2N2499	2N2500
NOTE 4: $V_{GS} =$	5 v	6 v	8 v	6 v
NOTE 5: $I_D =$	-1 ma	-2 ma	-5 ma	-1 ma

*Indicates JEDEC registered data.

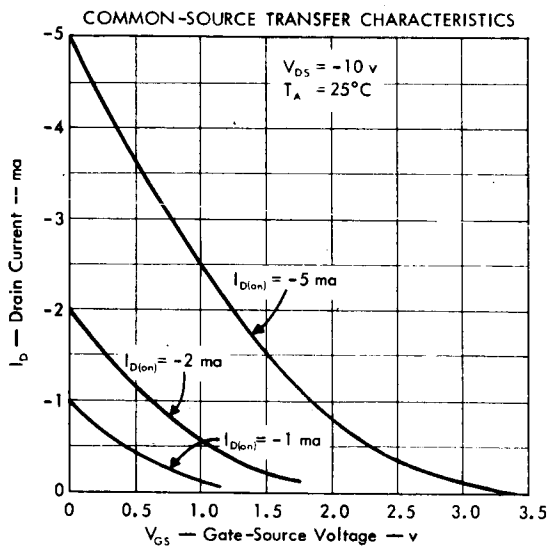
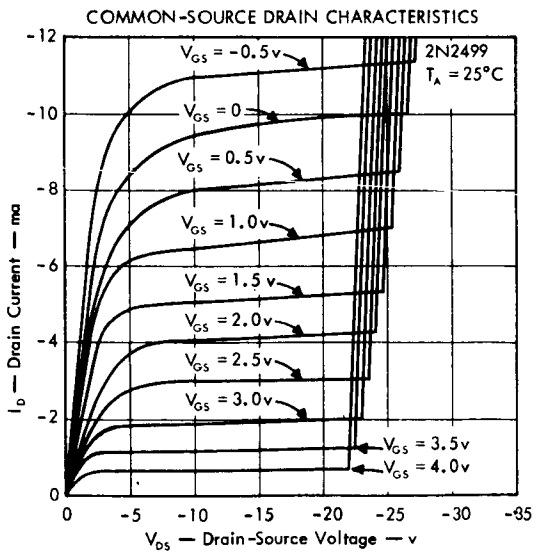
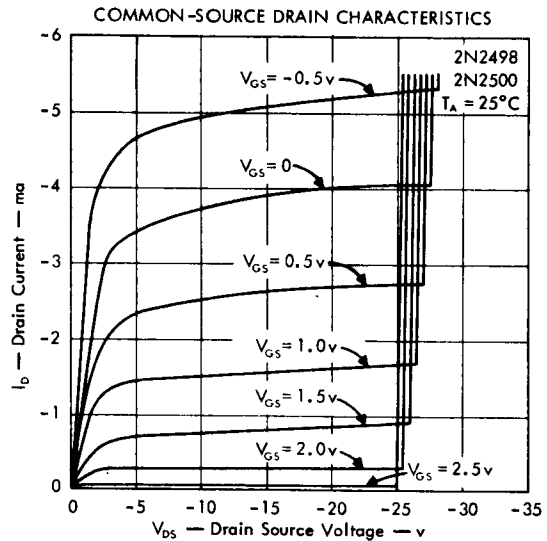
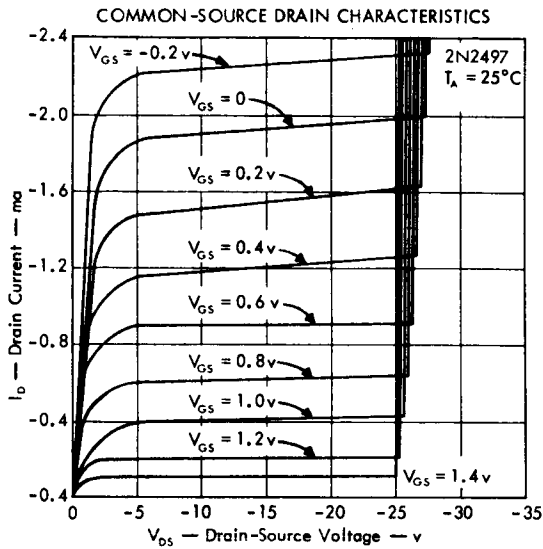
TYPES 2N2497, 2N2498, 2N2499, 2N2500
 BULLETIN NO. DL-5 633519, MAY 1963
 REPLACES BULLETINS NO. DL-5 627277 AND DL-5 627249, JUNE 1962



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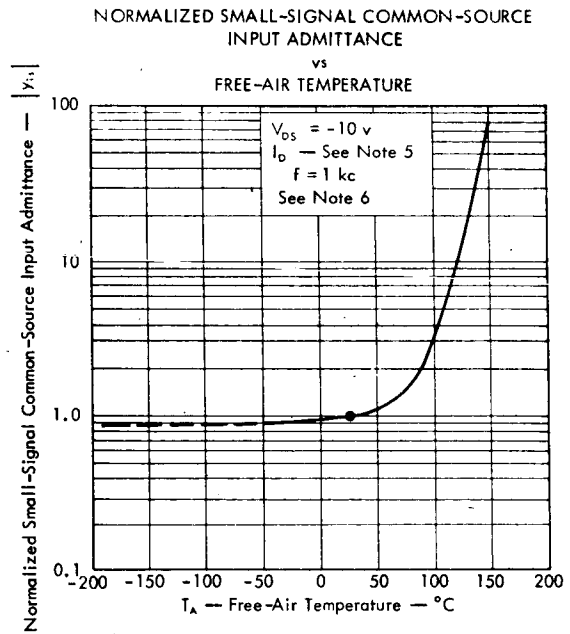
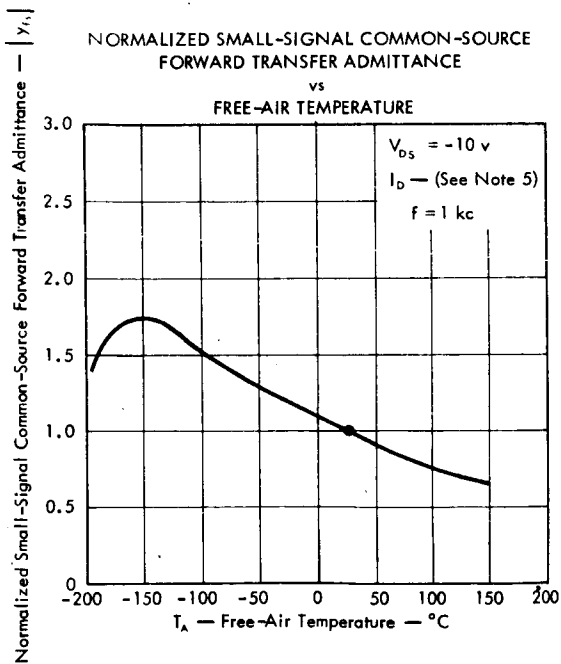
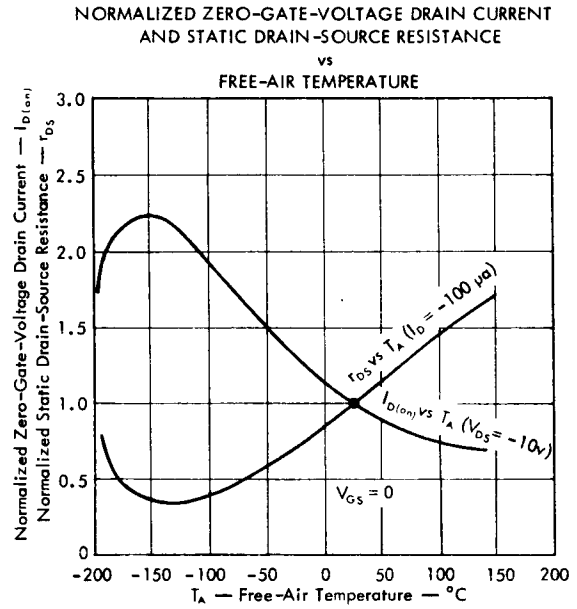
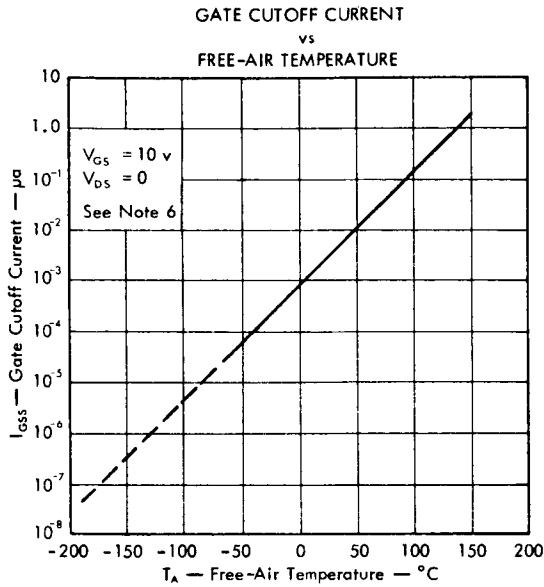
TYPES 2N2497, 2N2498, 2N2499, 2N2500

P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS



TYPES 2N2497, 2N2498, 2N2499, 2N2500 P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS

TYPICAL CHARACTERISTICS



NOTE 6: Dashed lines are extrapolations necessary because of test equipment limitation.

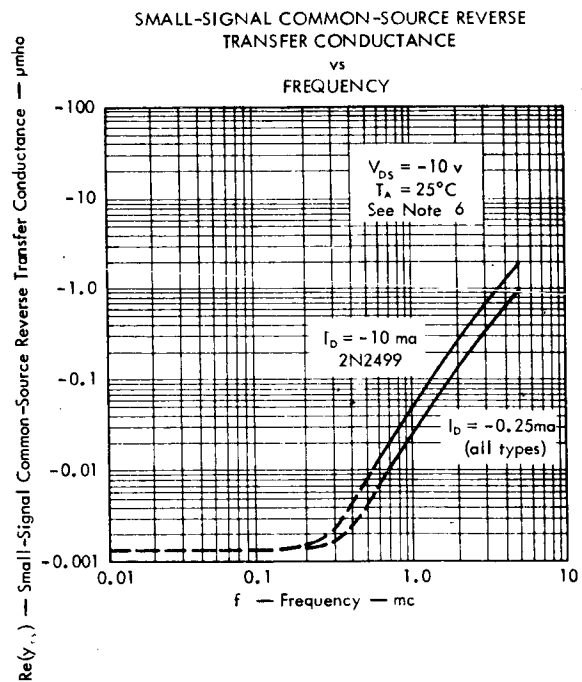
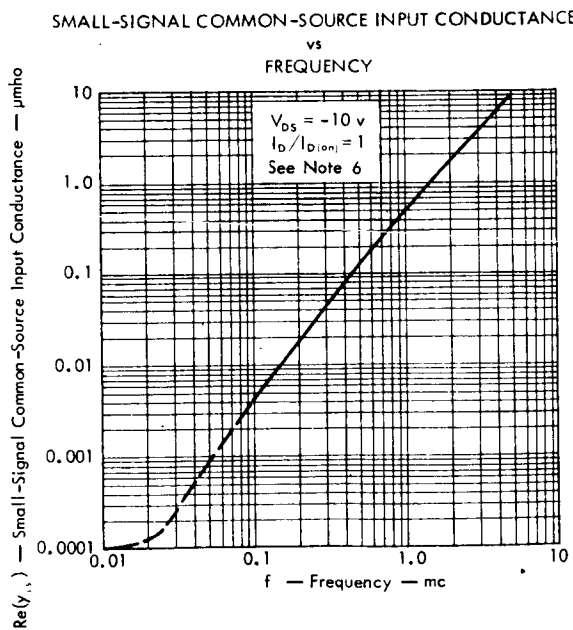
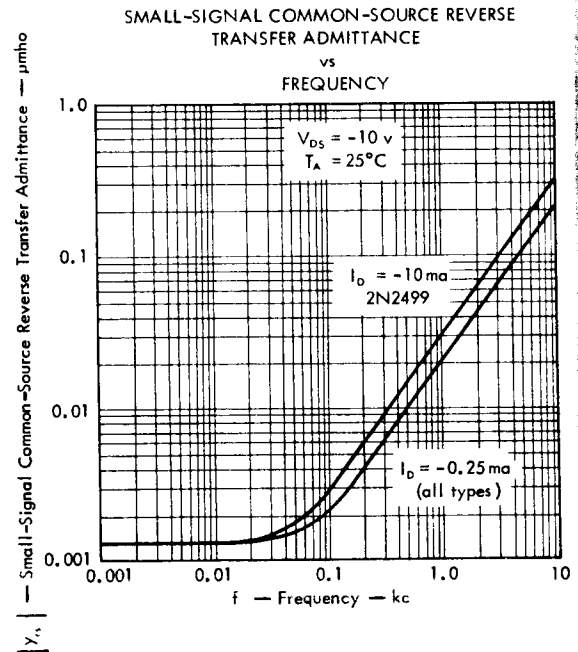
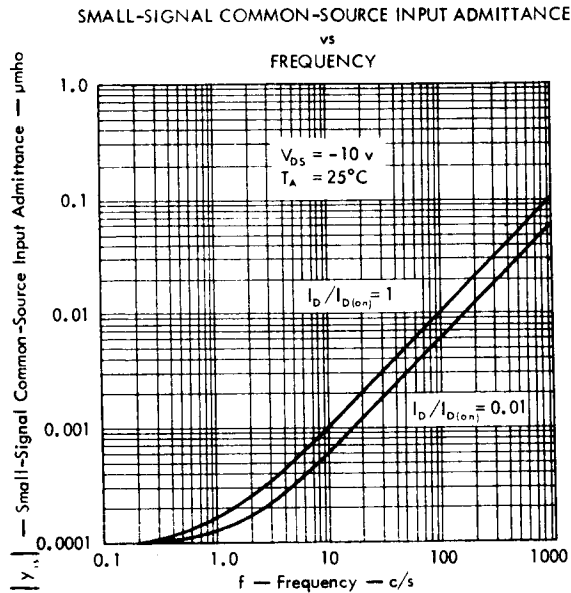


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TYPES 2N2497, 2N2498, 2N2499, 2N2500

P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS

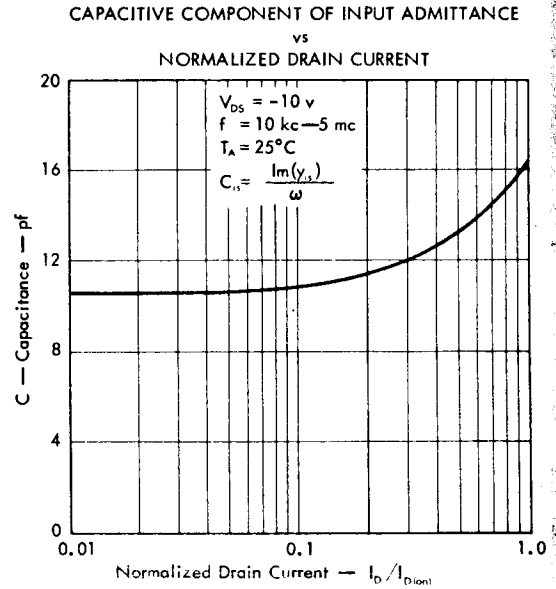
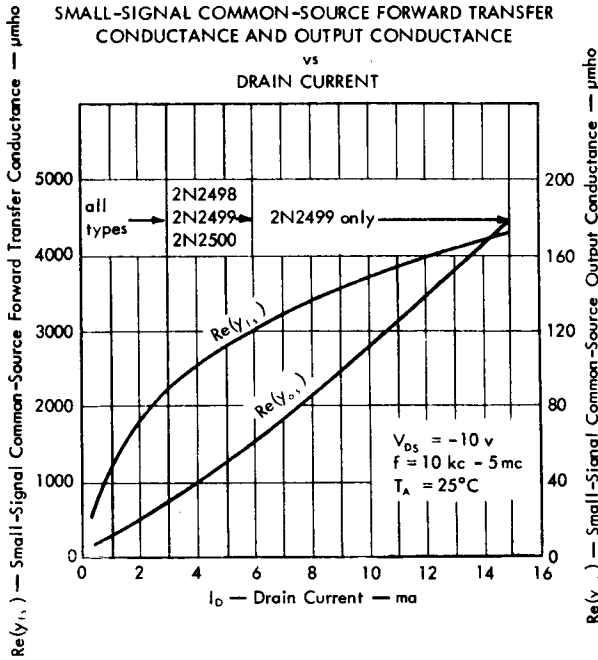
TYPICAL CHARACTERISTICS



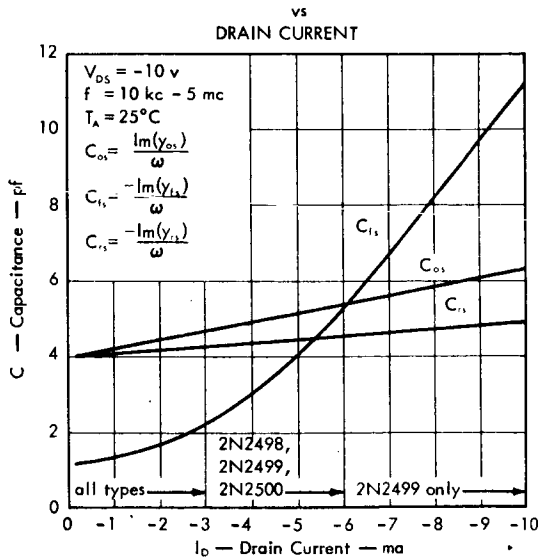
NOTE 6: Dashed lines are extrapolations necessary because of test equipment limitation.

TYPES 2N2497, 2N2498, 2N2499, 2N2500 P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS

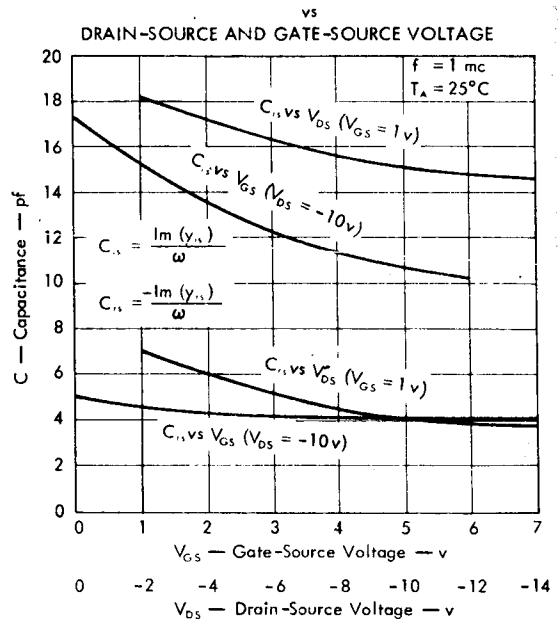
TYPICAL CHARACTERISTICS



CAPACITIVE COMPONENT OF OUTPUT, FORWARD TRANSFER, AND REVERSE TRANSFER ADMITTANCE



CAPACITIVE COMPONENT OF INPUT AND REVERSE TRANSFER ADMITTANCE

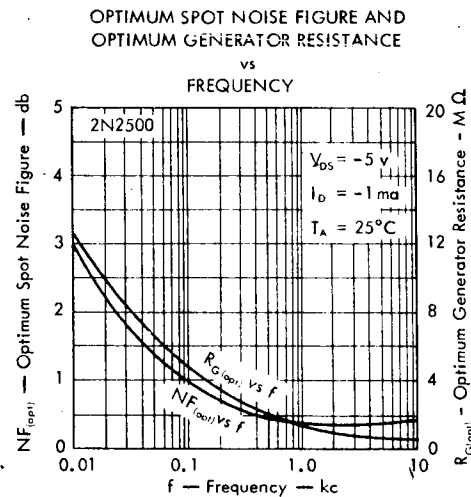
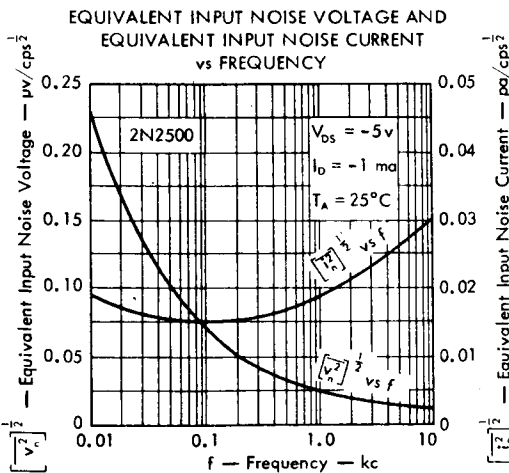
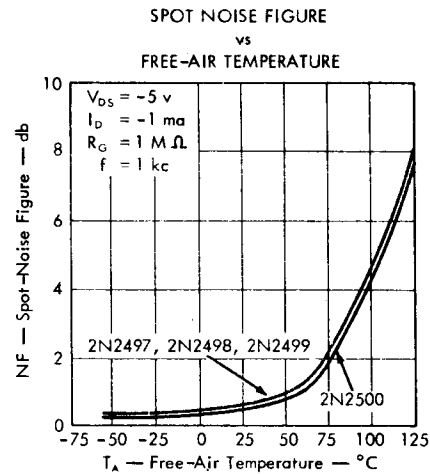
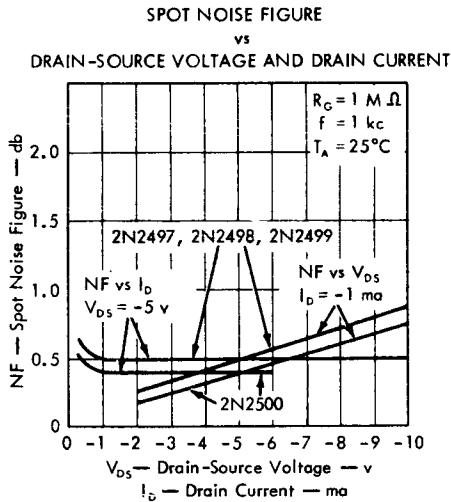
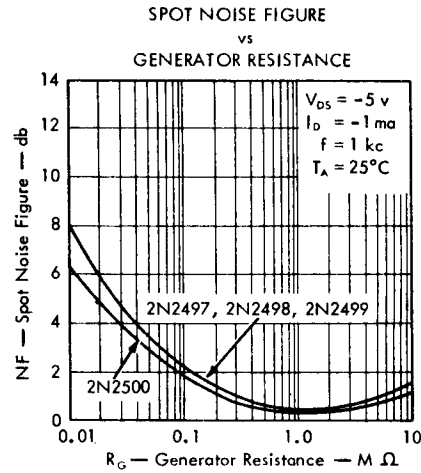
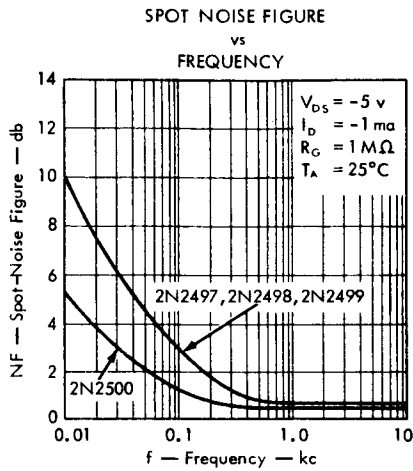


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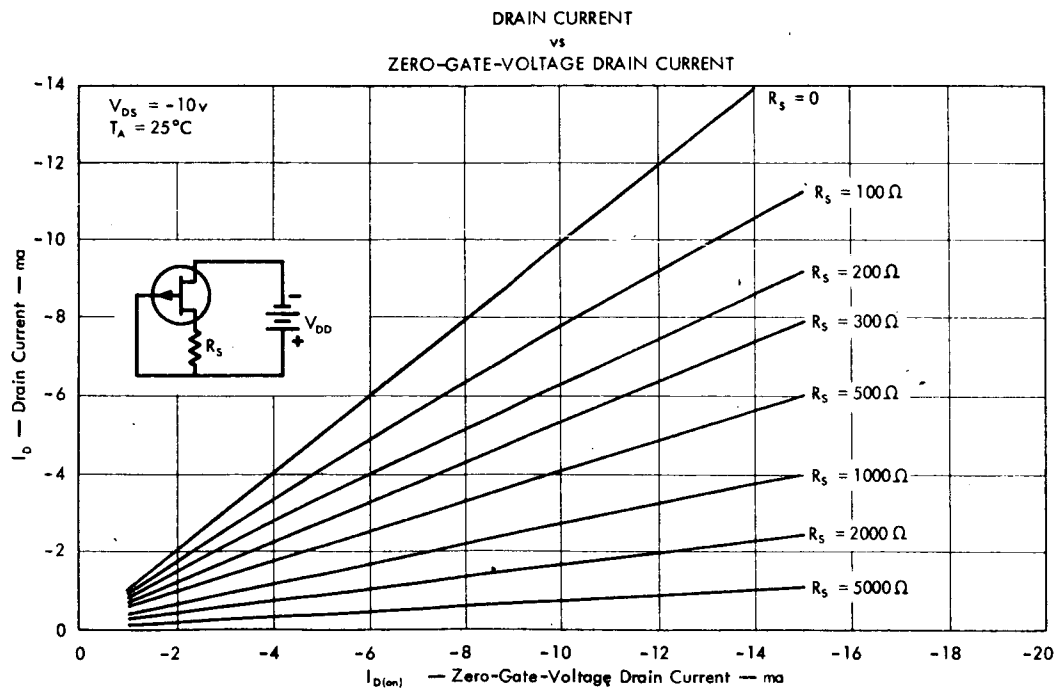
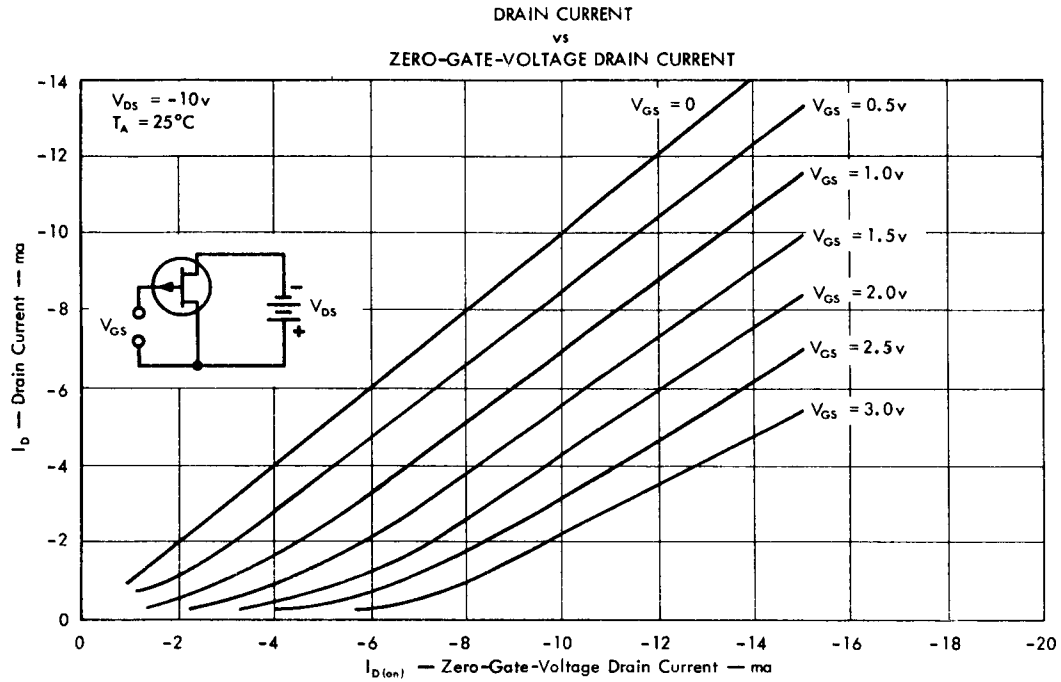
P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS

TYPICAL CHARACTERISTICS



TYPES 2N2497, 2N2498, 2N2499, 2N2500 P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS

BIAS DESIGN CURVES



TYPES 2N2497, 2N2498, 2N2499, 2N2500

P-CHANNEL DIFFUSED PLANAR SILICON FIELD-EFFECT TRANSISTORS

PARAMETER MEASUREMENT INFORMATION

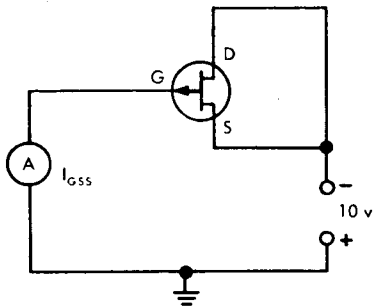
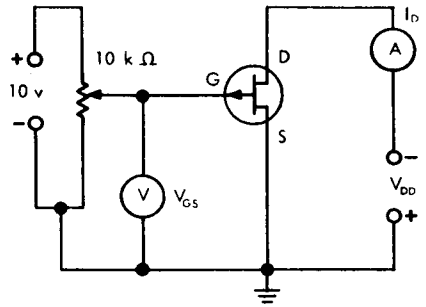


FIGURE 1 — GATE CUTOFF CURRENT TEST CIRCUIT



* FIGURE 2 — PINCH-OFF DRAIN CURRENT TEST CIRCUIT

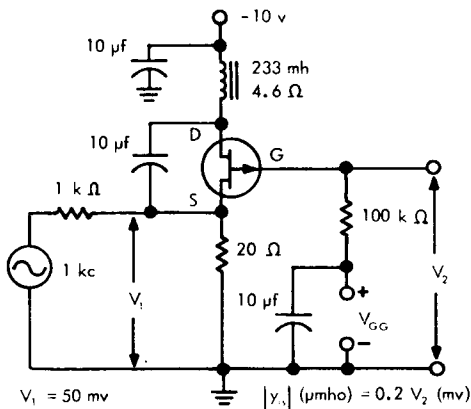


FIGURE 3 — INPUT ADMITTANCE TEST CIRCUIT

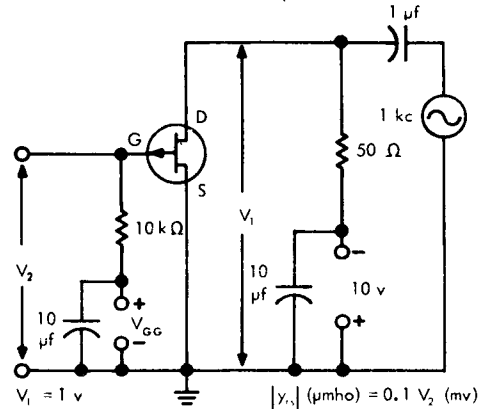
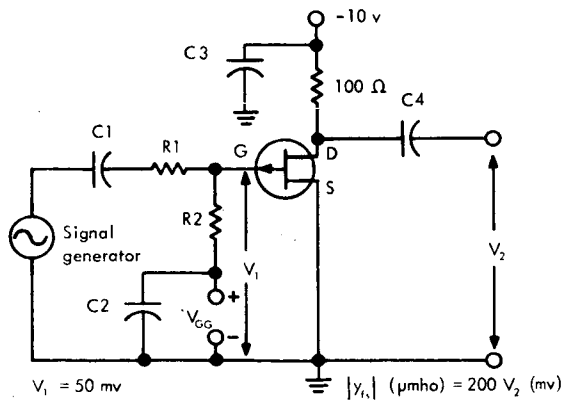


FIGURE 4 — REVERSE TRANSFER ADMITTANCE TEST CIRCUIT



f	R1	R2	C1	C2	C3	C4
1 kc	1 kΩ	10Ω	10μf	10 μf	10 μf	10 μf
10 mc	30Ω	20Ω	39pf	0.02μf	0.02 μf	0.02μf

FIGURE 5 — FORWARD TRANSFER ADMITTANCE TEST CIRCUIT

* Indicates JEDEC registered data.

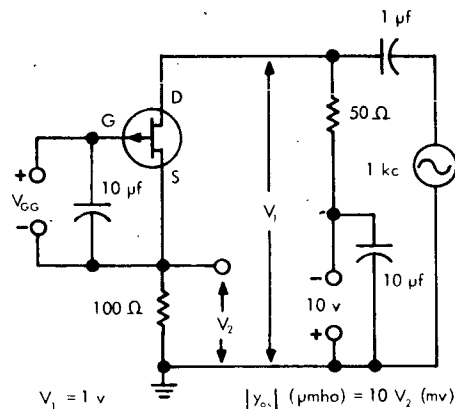


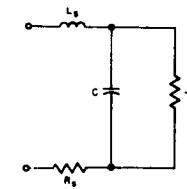
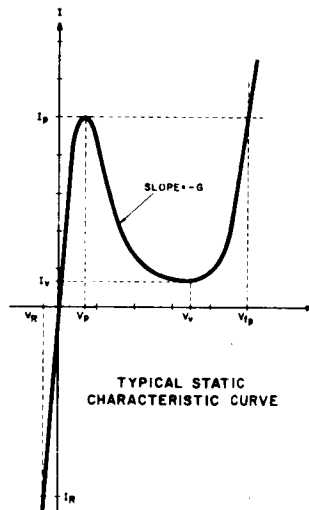
FIGURE 6 — OUTPUT ADMITTANCE TEST CIRCUIT

1N3219, 1N3219A

Outline Drawing No. 3

The 1N3219 and 1N3219A are germanium tunnel diodes which make use of the quantum mechanical tunneling phenomenon thereby attaining unique negative conductance characteristics and very high frequency performance.

These small stripline type packages are designed for microwave communications, radar, very high frequency amplifiers and oscillator applications. The very low series inductance plus controlled low capacity permits very high frequency performance in the S band.



EQUIVALENT CIRCUIT
(BIASED IN NEGATIVE
CONDUCTANCE REGION)

TYPICAL STATIC
CHARACTERISTIC CURVE

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS

Current

Forward (-55 to +100°C)	5	ma
Reverse (-55 to +100°C)	10	ma

Temperature

Storage	-55 to +100	°C
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ELECTRICAL CHARACTERISTICS: (25°C)

		Min.	Typ.	Max.	
Peak Point Current	I_p	2.0	2.2	2.4	ma
Valley Point Current	I_v		0.28	0.48	ma
Peak Point Voltage	V_p		60		mv
Valley Point Voltage	V_v		350		mv
Forward Voltage ($I_F = I_R = 2.2$ ma)	V_{FP}	450	500	600	mv
Reverse Voltage ($I_R = 2.2$ ma)	V_R		20		mv
Negative Conductance	-G	10	18	25	$\times 10^{-3}$ mho
Series Resistance	R_S		0.7	3.0	ohm
Series Inductance	L_S		0.3	0.5	nh
Total Capacity 1N3219	C	1.5	14	20	pf
Total Capacity 1N3219A	C	1.5	7	10	pf

Color Code: (counter clockwise on flange)
 1N3219 Orange-Red-Brown-White-Black
 1N3219A Orange-Red-Brown-White-Brown

APPENDIX VIII

PROPERTIES OF SYNTHANE G-10

Mechanical Properties

Resin	G-10 Epoxy
Tensile Strength, psi	
Lengthwise	35,000
Crosswise	30,000
Compression Strength, psi	
Flatwise	60,000
Edgewise	40,000
Flexural Strength psi (1/8" thick)	
Lengthwise	50,000
Crosswise	40,000
Modulus of Elasticity in Flexure, psi	
Lengthwise	2,500,000
Crosswise	2,000,000
Shear Strength, psi	19,000
Izod Impact, ft. lbs, per inch of notch	
Flatwise	7.0
Edgewise	5.5
Bond Strength, lbs.	

Electrical Properties

Resin	G-10 Epoxy
Dielectric Strength, VPM Perpendicular to laminations Short Time Test 1/16" 1/8"	500
Dissipation Factor, 1 megacycle Condition A	0.025
Dissipation Constant, 1 megacycle Condition A	5.8
Insulation Resistance, megohms Condition: 96 hrs., 90% relative humidity, 95° F	200,000
Arc Resistance, seconds	80
Water Absorption, %, 24 hrs. 1/16" 1/8" 1/2"	0.35 0.20 0.10

General Properties

Resin	G-10 Epoxy
Rockwell Hardness, M Scale	110
Specific Gravity	1.82
Coeff. of Ther. Expansion, Cm/Cm/°C	0.7×10^{-5}
Maximum Constant Operating Temperature, °F	300
Thickness	
Minimum	0.015"
Maximum	1"
Standard Colors	Natural (Gray White)
Standard Finishes	Semi Gloss

APPENDIX IX PROPERTIES OF TITANIUM ALLOY WIRE

Mechanical Properties	Guaranteed RT Minimum	Typical 400F	Strength 600F	(% RT) & Ductility	
				800F	1000F
Ultimate tensile strength, psi	125,000	92	87	92	76
Yield strength, 0.2% offset, psi	120,000	85	74	80	72
E1 in 2" (> 0.025" thick) pct	10	23	23	18	34
Reduction in area, percent	25				
Bend Radius	3T13.5T2				
Impact, Charpy V, ft-lb.					
Welded Bend Radius	3 T				
Hardness	RC 32-36				
Rupture, stress to produce in () hr, psi			0.5%		
Creep data, stress to produce () percent elongation in () hr., psi			500 hr	0.2%	
			131,000 3	500 hr	
			107,000 3		
Physical Properties					
Modulus of elasticity, psi, (10 ⁶) tension	15				
Modulus of elasticity, psi, (10 ⁶) torsion	6.2				
Density, lb/cu inch	0.176				
Melting Range, deg F					
Specific Electrical Resistivity	153 annealed				
micro ohms/cm/sq cm	142 STA				
Specific heat, Btu/lb/deg F	0.12 at RT to 200F				
Thermal conductivity, Btu/hr/sq ft/°F/ft	4 at room temperature				
	32-212 F				
	32-600 F				
Mean coefficient of thermal expansion per deg F, (10 ⁻⁶)	5.9				
	32-1000F				
	32-1200F				
	32-1500F				
Oxidation characteristics					
in air					
	400F	600F	800F	1000F	
	Good	Good	Good	Moderate	
	SHORT TIME				
	LONG TIME	Good	Moderate-Good	Moderate	